128Mb (8M x 16 bit) UtRAM

Document Title

8Mx16 bit Synchronous Burst Uni-Transistor Random Access Memory

Revision History

Revision No.	History	Draft Date	Remark
0.0	Initial - Design target	May.12,2006	Preliminary
1.0	Finalized - Added DPD period to guarantee default mode (min 4ms)	Mar.28,2007	Final

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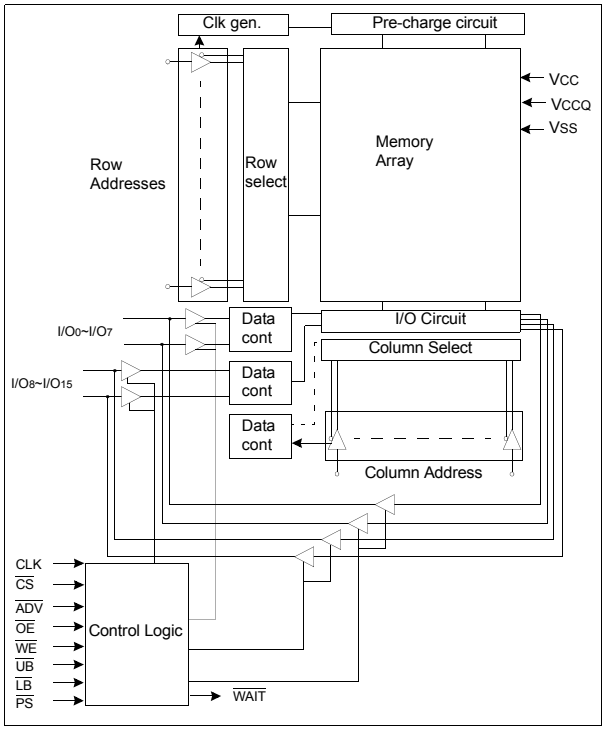
8M x 16 bit Synchronous Burst Uni-Transistor CMOS RAM

FEATURES & FUNCTION BLOCK DIAGRAM

- Process technology: CMOS
- Organization: 8M x 16 bit
- Power supply voltage: 1.7V~1.95V
- Three state outputs
- Supports MRS (Mode Register Set)
  - $\overline{PS}$ pin set up
  - Software set up
- Supports power saving modes
  - PAR (Partial Array Refresh)
  - DPD (Deep Power Down)
  - Internal TCSR
- Supports driver strength optimization
- Mode
  - Asynchronous read / Asynchronous write
  - Synchronous burst read / Asynchronous write
  - Synchronous burst read / Synchronous burst write
- Synchronous burst operation
  - Max. clock frequency : 104MHz
  - Fixed and Variable latency
  - 4 / 8 / 16 / 32 and Continuous burst
  - Wrap / No-wrap
  - Latency : 4(Variable) @ 104MHz
    3(Variable) @ 80MHz
    2(Variable) @ 66MHz
  - Burst stop
  - Burst read suspend
  - Burst write data masking



GENERAL PHYSICAL SPECIFICATIONS

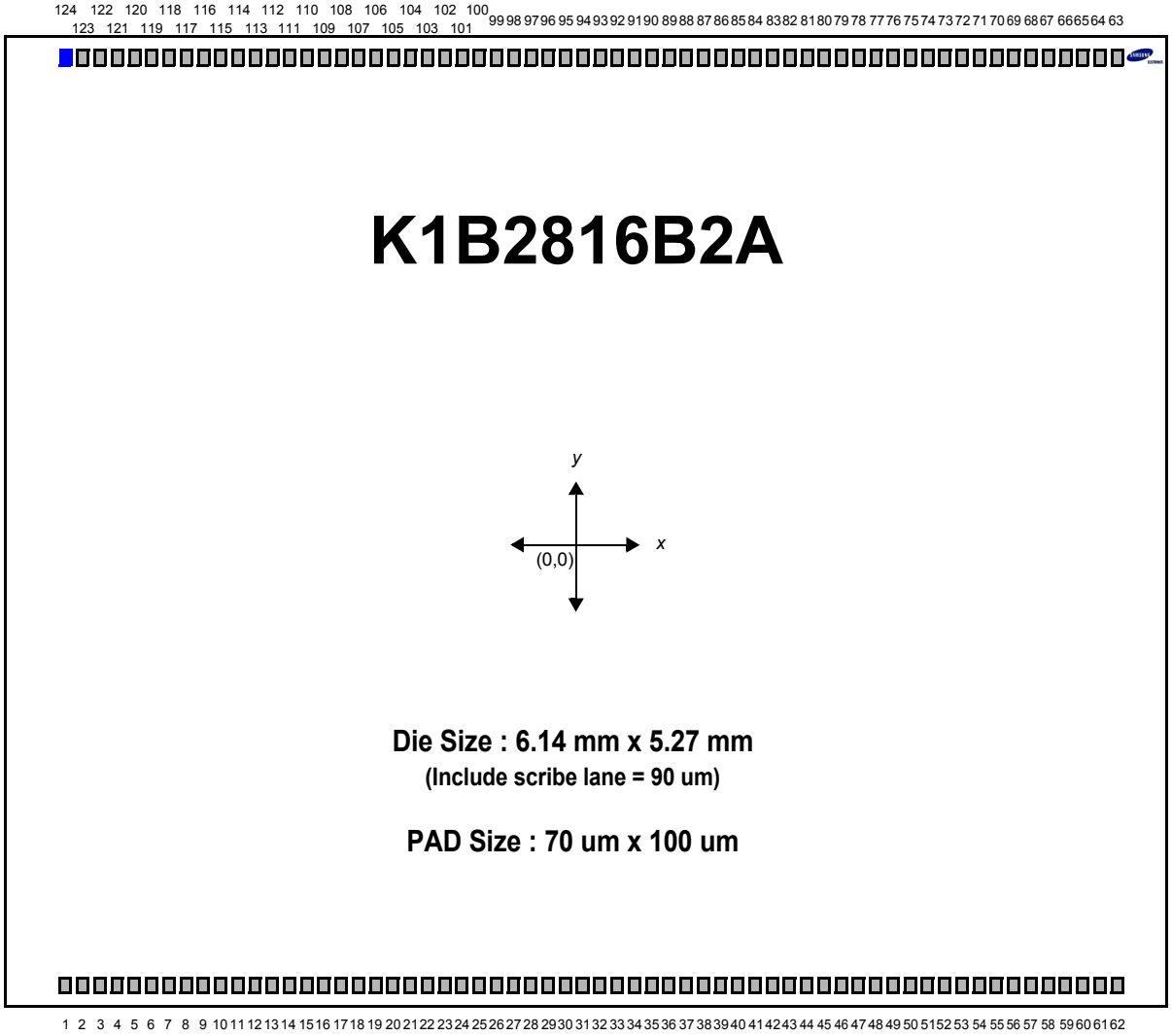
- Backside die surface of polished bare silicon
- Typical Die Thickness = 725μm
- Typical top-level metallization:
  - Metal: 8K Angstroms thickness Al.
    0.2% Si + 0.5% Cu
- Topside Passivation:
  - 6K Angstroms SiN
  - 5μm ± 0.5μm Polyimide
- Typical Pad Size: 70μm x 100μm
- Die Size: 6.14mm x 5.27mm including scribe lane
- Wafer diameter: 8 inch
  Net die/Wafer: 780ea

OPTIONS

- K1/W1: DC Probed Die/Wafer @ Hot Temp
- K2/W2: DC/AC Probed Die/Wafer @ Hot Temp
- K3/W3: DC/AC Probed Die/Wafer @ Hot and Cold Temp

BONDING INSTRUCTIONS

The 128Mb UtRAM A-die has total 124 pads. Refer to the bond pad location and identification table for X, Y coordinates.



* #124 is monitor pad that is needed for Samsung use only, it may looks different color from other pads and should not be bonded.

BOND PAD LOCATION AND IDENTIFICATION

Unit : um

PAD#	FUNCTION	X	Y	PAD#	FUNCTION	X	Y
1	DNU	-2575.9	-2487.5	63	DNU	2575.9	2490.6
2	DNU	-2490.3	-2487.5	64	DNU	2490.3	2490.6
3	DNU	-2404.7	-2487.5	65	A16	2404.7	2490.6
4	DNU	-2319.2	-2487.5	66	A15	2319.2	2490.6
5	DNU	-2233.6	-2487.5	67	A14	2233.6	2490.6
6	VSS	-2148.1	-2487.5	68	A13	2148.1	2490.6
7	VSSQ	-2062.5	-2487.5	69	A12	2062.5	2490.6
8	VCC	-1976.9	-2487.5	70	A11	1976.9	2490.6
9	VCC	-1891.4	-2487.5	71	A10	1891.4	2490.6
10	VSS	-1805.8	-2487.5	72	VCC	1805.8	2490.6
11	IO0	-1720.3	-2487.5	73	VCC	1720.3	2490.6
12	IO8	-1634.7	-2487.5	74	VSS	1634.7	2490.6
13	VCCQ	-1549.1	-2487.5	75	VSS	1549.1	2490.6
14	VSSQ	-1463.6	-2487.5	76	A9	1463.6	2490.6
15	IO1	-1378.0	-2487.5	77	A8	1378.0	2490.6
16	IO9	-1292.5	-2487.5	78	VCC	1292.5	2490.6
17	VCC	-1206.9	-2487.5	79	VCC	1206.9	2490.6
18	VCC	-1121.3	-2487.5	80	VSS	1121.3	2490.6
19	VSS	-1035.8	-2487.5	81	VSS	1035.8	2490.6
20	VSS	-950.2	-2487.5	82	VSS	950.2	2490.6
21	VCCQ	-864.7	-2487.5	83	DNU	864.7	2490.6
22	IO2	-779.1	-2487.5	84	A22	779.1	2490.6
23	IO10	-693.5	-2487.5	85	A21	693.5	2490.6
24	VCCQ	-608.0	-2487.5	86	DNU	608.0	2490.6
25	VSSQ	-522.4	-2487.5	87	A20	522.4	2490.6
26	IO3	-436.9	-2487.5	88	CLK	436.9	2490.6
27	IO11	-351.3	-2487.5	89	$\overline{WE}$	351.3	2490.6
28	$\overline{OE}$	-265.7	-2487.5	90	$\overline{ADV}$	265.7	2490.6
29	VCCQ	-180.2	-2487.5	91	$\overline{PS}$	180.2	2490.6
30	VCC	-94.6	-2487.5	92	VSS	94.6	2490.6
31	VCC	-9.1	-2487.5	93	VCC	9.1	2490.6
32	CLK	76.5	-2487.5	94	DNU	-76.5	2490.6
33	VSS	162.1	-2487.5	95	$\overline{UB}$	-162.1	2490.6
34	VSS	247.6	-2487.5	96	$\overline{LB}$	-247.6	2490.6
35	VSSQ	333.2	-2487.5	97	$\overline{CS}$	-333.2	2490.6
36	IO4	418.8	-2487.5	98	A19	-418.8	2490.6
37	IO12	504.3	-2487.5	99	DNU	-504.3	2490.6
38	VSSQ	589.9	-2487.5	100	A18	-589.9	2490.6
39	VCCQ	675.4	-2487.5	101	A17	-675.4	2490.6
40	IO5	761.0	-2487.5	102	VSS	-761.0	2490.6
41	IO13	846.6	-2487.5	103	VSS	-846.6	2490.6
42	VCCQ	932.1	-2487.5	104	VCC	-932.1	2490.6
43	VSSQ	1017.7	-2487.5	105	VCC	-1017.7	2490.6
44	DNU	1103.2	-2487.5	106	VCC	-1103.2	2490.6
45	VSS	1188.8	-2487.5	107	A7	-1188.8	2490.6
46	VSS	1274.4	-2487.5	108	DNU	-1274.4	2490.6
47	VCC	1359.9	-2487.5	109	DNU	-1359.9	2490.6
48	VCC	1445.5	-2487.5	110	A6	-1445.5	2490.6
49	IO6	1531.0	-2487.5	111	A5	-1531.0	2490.6
50	IO14	1616.6	-2487.5	112	A4	-1616.6	2490.6
51	VSSQ	1702.2	-2487.5	113	A3	-1702.2	2490.6
52	VCCQ	1787.7	-2487.5	114	DNU	-1787.7	2490.6
53	IO7	1873.3	-2487.5	115	VSS	-1873.3	2490.6
54	IO15	1958.8	-2487.5	116	VSS	-1958.8	2490.6
55	$\overline{WAIT}$	2044.4	-2487.5	117	A2	-2044.4	2490.6
56	VCC	2129.9	-2487.5	118	VCC	-2129.9	2490.6
57	VCC	2215.5	-2487.5	119	VCC	-2215.5	2490.6
58	VCCQ	2301.1	-2487.5	120	A1	-2301.1	2490.6
59	VSS	2386.6	-2487.5	121	A0	-2386.6	2490.6
60	VSSQ	2472.2	-2487.5	122	DNU	-2472.2	2490.6
61	VSS	2557.7	-2487.5	123	DNU	-2557.7	2490.6
62	DNU	2643.3	-2487.5	124	DNU	-2643.3	2490.6

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PAD DESCRIPTION

Name	Function	Type	Description
CLK	Clock	Input	Synchronizes the memory to the system operating frequency during synchronous operations. Commands are referenced to CLK.
$\overline{ADV}$	Address Valid	Input	Indicates that a valid address is present on the address inputs. Addresses can be latched on the rising edge of $\overline{ADV}$ during asynchronous READ and WRITE operations.
$\overline{PS}$	Mode Register set	Input	$\overline{PS}$ low enables Mode Register to be set and enables either PAR or DPD to be set.
$\overline{CS}$	Chip Select	Input	$\overline{CS}$ low enables the chip to be active $\overline{CS}$ high disables the chip and puts it into standby mode or deep power down mode.
$\overline{OE}$	Output Enable	Input	Enables the output buffers when LOW. when $\overline{OE}$ is HIGH, the output buffers are disabled.
$\overline{WE}$	Write Enable	Input	$\overline{WE}$ low enables the chip to start writing the data
$\overline{LB}$	Lower Byte ($I/O_{0\sim7}$)	Input	$\overline{UB}$ ($\overline{LB}$) low enables upper byte (lower byte) to allow data Input/output from I/O buffers.
$\overline{UB}$	Upper Byte ($I/O_{8\sim15}$)	Input	
A0~A22	Address 0 ~ Address 22	Input	Inputs for addresses during READ and WRITE operations. Addresses are internally latched during READ and WRITE cycles.
I/O0~I/O15	Data Inputs / Outputs	Input/Output	Depending on $\overline{UB}$ or $\overline{LB}$ status, word(16-bit, $\overline{UB}$ & $\overline{LB}$ low) data, upper byte(8-bit, $\overline{UB}$ low & $\overline{LB}$ high) data or lower byte(8-bit, $\overline{LB}$ low & $\overline{UB}$ high) data is loaded
VCC	Voltage Source	Power	Device Power supply. Power supply for device core operation.
VCCQ	I/O Voltage Source	Power	I/O Power supply. Power supply for input/output buffers.
VSS	Ground Source	GND	Ground for device operation
VSSQ	I/O Ground Source	GND	Ground for Input/Output buffers
$\overline{WAIT}$	Valid Data Indicator	Output	The $\overline{WAIT}$ signal is output signal indicating the status of the data on the bus whether or not it is valid. $\overline{WAIT}$ is asserted when a burst crosses a word-line boundary. $\overline{WAIT}$ is asserted and should be ignored during asynchronous and page mode operations.
DNU	Do Not Use	-	-
MRS Option	MRS input type select	Input	MRS input type select option between '$\overline{PS}$ pin & Software' and 'Software only' type. '$\overline{PS}$ pin MRS & Software MRS' type is selected when this pad is floating and can not guarantee default modes[1]. 'Software MRS only' type is selected when this pad is connected to Vss and can guarantee default modes[1].

1. Default modes : Asynchronous 4 page Read and Asynchronous Write / DPD disable / PAR disable
   Default modes are automatically set after power up or DPD exit.

FUNCTIONAL SPECIFICATIONS

There are 3 classifications for SAMSUNG die and wafers products, which are K1, K2, and K3 for die and W1, W2 and W3 for wafer, respectively. Each die and wafer support dedicated characteristics and probe the electrical parameters within their specifications. Followings are brief information for die and wafer classifications. Please refer to packaged specifications for more information but these parameters are not guaranteed at bare die and wafer.

• K1 LEVEL DIE OR W1 LEVEL WAFER

The DC parameters are measured by specification for K1 level die or W1 level wafer. The DC parameters measured at 70°C temperature, which called 'Hot DC Sorting'. Other parameters are not guaranteed and warranted including device reliability. Please refer to qualification report for device reliability and package level datasheets for electrical parameters.

• K2 LEVEL DIE OR W2 LEVEL WAFER

The DC parameters and selected AC parameters are measured with for K2 level die or W2 level wafer. The DC characteristics of K2 die and W2 wafer is tested based on DC specifications of K1 level die and W1 level wafer. The DC and specified AC parameters are tested at 70°C temperature, which called 'Hot DC & Selective AC Sorting'. Other parameters are not guaranteed and warranted including device reliability. Please refer to qualification report for device reliability and package level datasheets for electrical parameters.

K2 level die and W2 level wafer probe following AC parameter.

- tRC, tAA, tCO
- tWC, tCW

• K3 LEVEL DIE OR W3 LEVEL WAFER

More selected AC parameters than those of K2 and W2 are tested by specifications. Especially, the cold and hot temperature, -40°C and 85°C is applied while being tested electrical parameters based on K2 level die and W2 level wafer specifications. Other parameters are not guaranteed and warranted including device reliability. Please refer to qualification report for device reliability and package level datasheets for electrical parameters.

K3 level die and W3 level wafer probe following AC parameter.

- tRC, tAA, tCO, tOE
- tWC, tCW, tAS, tAW, tWP, tDW, tDH

PACKING

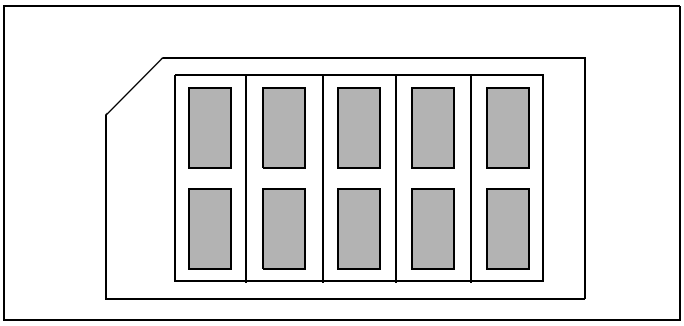
Individual device will be packed in anti-static trays.

• Chip Trays: A 2-inch square waffle style carrier for die with separate compartments for each die. Commonly referred to as a waffle pack, each tray has a cavity size selected for the device that allows for easy loading and unloading and prevents rotation. The tray itself is made of conductive material to reduce the danger of damage to the die from electrostatic discharge.

The chip carriers will be labeled with the following information :

• SAMSUNG wafer lot number
• SAMSUNG part number
• Quantity

• Jar Packing: Jar packing is made by Samsung Electronics and used by many customers that we deliver the requested die as wafer. The pack is consisted of clean paper to wrap the wafer, high cushioned sponge between wafers and hardly fragile plastic box with sponge. Each pack has typically 25 wafers and then several packs are put into larger box depending on amounts of wafers.



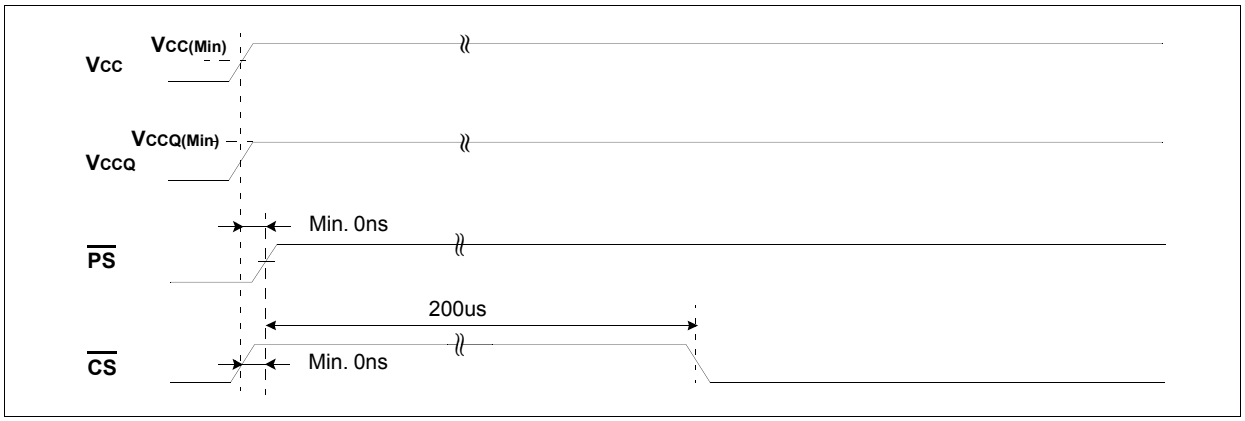
Die orientation in chip carriers

STORAGE AND HANDLING

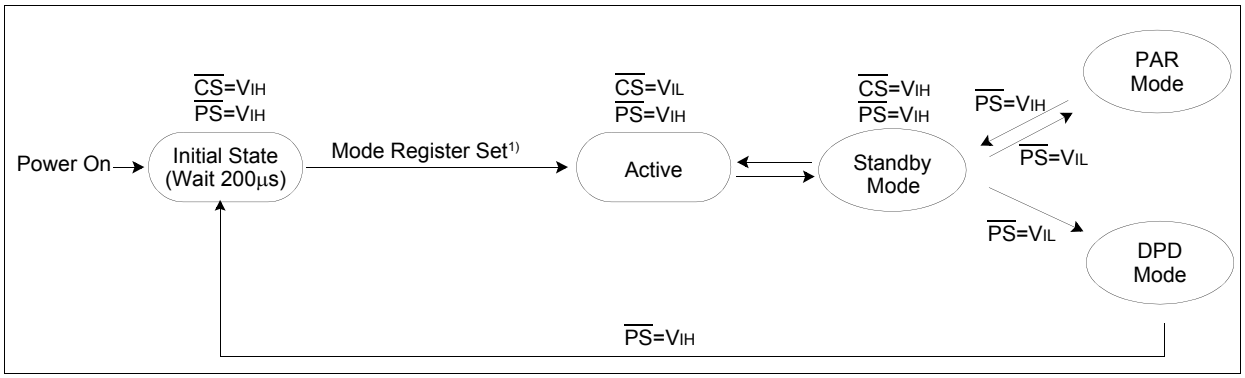
SAMSUNG recommends the die stored in a controlled environment with filtered nitrogen. The carrier must be opened at ESD safe environment when inspection and assembly.

POWER UP SEQUENCE

After V_{CC} and V_{CCQ} reach minimum operating voltage(1.7V), drive $\overline{CS}$ High first and then drive $\overline{PS}$ High. Then the device gets into the Power Up mode. Wait for minimum 200μs to get into the normal operation mode. During the Power Up mode, the standby current can not be guaranteed. To get the stable standby current level, at least one cycle of active operation should be implemented regardless of wait time duration. To get the appropriate device operation, be sure to keep the following power up sequence. MODE1(Asynchronous Read / Asynchronous Write) is set up after power up, but this mode is not always guaranteed.



MODE STATE MACHINE



1) Refer to MRS(Mode Register Set).

ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Ratings	Unit
Voltage on any pin relative to Vss	V_{IN}, V_{OUT}	-0.2 to V_{CCQ}+0.3V	V
Power supply voltage relative to Vss	V_{CC}, V_{CCQ}	-0.2 to 2.5V	V
Power Dissipation	P_D	1.0	W
Storage temperature	T_{STG}	-65 to 150	°C
Operating Temperature	T_A	-40 to 85	°C

1) Stresses greater than "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to be used under recommended operating condition. Exposure to absolute maximum rating conditions longer than 1 second may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

Item	Symbol	Min	Typ	Max	Unit
Power supply voltage(Core)	V_{CC}	1.7	1.8	1.95	V
Power supply voltage(I/O)	V_{CCQ}	1.7	1.8	1.95	V
Ground	V_{SS}, V_{SSQ}	0	0	0	V
Input high voltage	V_{IH}	0.8 x V_{CCQ}	-	V_{CCQ}+0.2[2]	V
Input low voltage	V_{IL}	-0.2[3]	-	0.4	V

1. T_A=-40 to 85°C, otherwise specified.
2. Overshoot: V_{CCQ} +1.0V in case of pulse width ≤20ns. Overshoot is sampled, not 100% tested.
3. Undershoot: -1.0V in case of pulse width ≤20ns. Undershoot is sampled, not 100% tested.

CAPACITANCE (f=1MHz, T_A=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C_{IN}	V_{IN}=0V	-	8	pF
Input/Output capacitance	C_{IO}	V_{IO}=0V	-	8	pF

DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions			Min	Typ	Max	Unit
Input Leakage Current	I_{LI}	V_{IN}=Vss to V_{CCQ}			-1	-	1	µA
Output Leakage Current	I_{LO}	$\overline{CS}$=V_{IH}, $\overline{PS}$=V_{IH}, $\overline{OE}$=V_{IH} or $\overline{WE}$=V_{IL}, V_{IO}=Vss to V_{CCQ}			-1	-	1	µA
Average Operating Current(Async)	I_{CC2}	Cycle time=70ns, I_{IO}=0mA[4], 100% duty, $\overline{CS}$=V_{IL}, $\overline{PS}$=V_{IH}, V_{IN}=V_{IL} or V_{IH}			-	-	35	mA
	I_{CC2P}	Cycle time=tRC+3tPC, I_{IO}=0mA[4], 100% duty, $\overline{CS}$=V_{IL}, $\overline{PS}$=V_{IH}, V_{IN}=V_{IL} or V_{IH}			-	-	20	mA
Average Operating Current(Sync)	I_{CC3}	Burst Length 4, Latency 5, 80MHz, I_{IO}=0mA[4], Address transition 1 time, $\overline{CS}$=V_{IL}, $\overline{PS}$=V_{IH}, V_{IN}=V_{IL} or V_{IH}			-	-	35	mA
Output Low Voltage	V_{OL}	I_{OL}=0.1mA			-	-	0.2	V
Output High Voltage	V_{OH}	IOH=-0.1mA			1.4	-	-	V
Standby Current(CMOS)	I_{SB1}[1]	$\overline{CS}$≥V_{CCQ}-0.2V, $\overline{PS}$≥V_{CCQ}-0.2V, Other inputs=Vss or V_{CCQ} (Toggle is not allowed)[5]	< 40°C		-	-	135	µA
			< 85°C		-	-	250	µA
Partial Refresh Current	I_{SBP}[2]	$\overline{PS}$≤0.2V, $\overline{CS}$≥V_{CCQ}-0.2V, Other inputs=Vss or V_{CCQ} (Toggle is not allowed)[5]	< 40°C	1/2 Block	-	-	125	µA
				1/4 Block	-	-	120	
			< 85°C	1/2 Block	-	-	220	µA
				1/4 Block	-	-	205	
Deep Power Down Current	I_{SBD}	$\overline{PS}$≤0.2V, $\overline{CS}$≥V_{CCQ}-0.2V, Other inputs=Vss or	< 85°C		-	-	10	µA

1. I_{SB1} is measured after 60ms after $\overline{CS}$ high. CLK should be fixed at high or at Low.
2. Full Array Partial Refresh Current(I_{SBP}) is same as Standby Current(I_{SB1}).
3. Internal TCSR (Temperature Compensated Self Refresh) is used to optimize refresh cycle below 40°C.
4. I_{IO}=0mA; This parameter is specified with the outputs disabled to avoid external loading effects.
5. V_{IN}=0V; all inputs should not be toggle.
6. Clock should not be inserted between $\overline{ADV}$ low and $\overline{WE}$ low during Write operation.

MRS (MODE REGISTER SET)

The mode registers store the values for the various modes to make UtRAM suitable for a various applications through MRS. There are two ways to perform MRS. One is $\overline{PS}$ pin MRS and the other is Software MRS. The mode registers have lots of fields and each field consists of several options. Refer to the Table below for detailed Mode Register Setting. A19~A22 addresses are "Don't care" in Mode Register Setting.

MRS CODE

MRS code consists of 12 categories and several options in each category. RARS, PARA, PAR and DPD are related to power saving, BL, WC, Latency, Wrap, WP, MS and IL are related to bus operation and DS is related to device output impedance.

Mode Register Setting according to field of function

Address	A18	A17~A16	A15~A14	A13	A12	A11~A9	A8	A7~A5	A4	A3	A2	A1~A0
Function	IL	DS	MS	WP	Wrap	Latency	WC	BL	DPD	PAR	PARA	PARS

Initial Latency		Driver Strength			Mode Select		
A18	IL	A17	A16	DS	A15	A14	MS[1]
0	Fixed	0	0	Full Drive	0	0	**Mode 1**(Async. 4 Page Read / Async. Write)
1	Variable	0	1	**1/2 Drive**	0	1	Mode 2(Sync. Burst Read / Async. Write)
		1	0	1/4 Drive	1	0	Mode 3(Sync. Burst Read / Sync. Burst Write)

$\overline{WAIT}$ Polarity		Wrap		Latency Count				$\overline{Wait}$ Configuration		Burst Length			
A13	WP[1]	A12	Wrap	A11	A10	A9	Latency	A8	WC	A7	A6	A5	BL
0	Low Enable	0	Wrap	1	0	0	2	0	One clock prior	0	1	0	4 word
1	High Enable	1	No-Wrap	0	0	0	3	1	At data	0	1	1	8 word
				0	0	1	4			1	0	0	16 word
				0	1	0	5			1	0	1	32 word
				0	1	1	6			1	1	1	Continuous[2]
				1	0	1	7						
				1	1	0	8						
				1	1	1	9						

Deep Power Down		Partial Array Refresh		PAR Array		PAR Size		
A4	DPD	A3	PAR	A2	PARA	A1	A0	PARS
0	DPD Enable	0	PAR Enable	0	Bottom Array	0	0	Full Array
1	**DPD Disable**	1	**PAR Disable**	1	Top Array	1	0	1/2 Array
						1	1	1/4 Array

[Note]
- A19~A22 addresses are "Don't care" & reserved for future use.
- The default modes are set automatically after power up or DPD exit.
  * Default modes: Async. Read and Async. Write / DPD disable / PAR disable
  * Once the device enters DPD mode, the DPD mode should last over 4ms or the default mode can not be guaranteed after DPD exit.

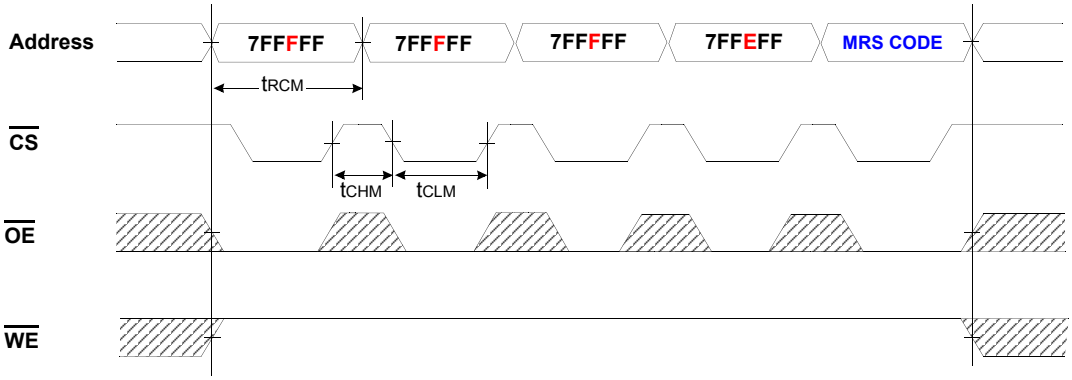
- Mode Change Rules.
  Mode1 to Mode2 (or vice-versa) : No limitation
  Mode1 to Mode3 : 1 dummy write(to any address with any data) is necessary before setting Mode3
  * Dummy write: Dummy write timing is just the same with normal write timing. It is necessary because 'Late write' is applied to Asynchronous write as in Mode1.
  * Late write: The data that is latched in previous write cycle is written in the address that is also latched in previous write cycle when Write starts. And current data and address are latched when Write ends. ($\overline{WE}$ high or $\overline{CS}$ high, whichever comes first)
  Mode3 to Mode1 : 1 dummy write is necessary before setting Mode1
  * Dummy write: The data and the address should be the same with those which are used during Mode1 to Mode3 transition.

1) WP[0]; The data is available when $\overline{WAIT}$ signal is High. All the timings in this spec are illustrated based on this mode.
   WP[1]; The data is available when $\overline{WAIT}$ signal is Low.
2) Refresh command will be denied during continuous operation. $\overline{CS}$ low should not be longer than tBC(max. 1.2us)

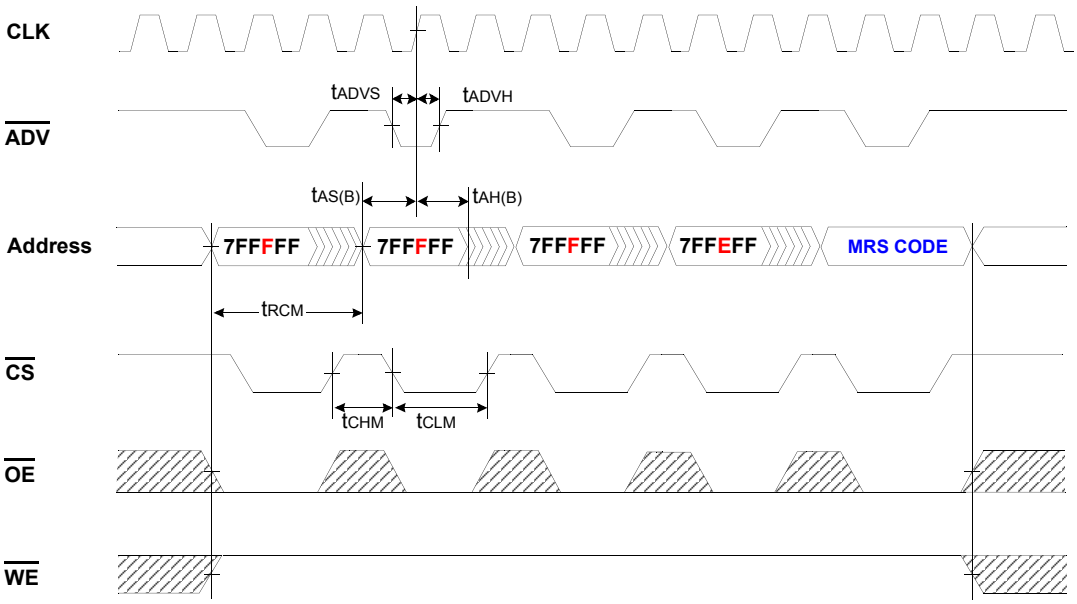
MRS TIMING WAVEFORM (SOFTWARE)

Software MRS timing consists of 5 Read cycles. Each cycle is normal Read cycle. $\overline{CS}$ pin should be toggling between cycles. 1st, 2nd and 3rd cycle should be 7FFFFF(h), 4th cycle should be 7FFEFF(h) and 5th cycle should be MRS code

Asynch. Mode Clock, $\overline{ADV}$, $\overline{UB}$ and $\overline{LB}$ = Don't care, $\overline{WAIT}$=High-Z, $\overline{PS}$=V_{IH}



Synch. Mode $\overline{UB}$ and $\overline{LB}$ = Don't care, $\overline{PS}$=V_{IH}



Note) Above timing and address condition should not be used in the normal operation. The above condition should be used only for the mode register setting purpose.

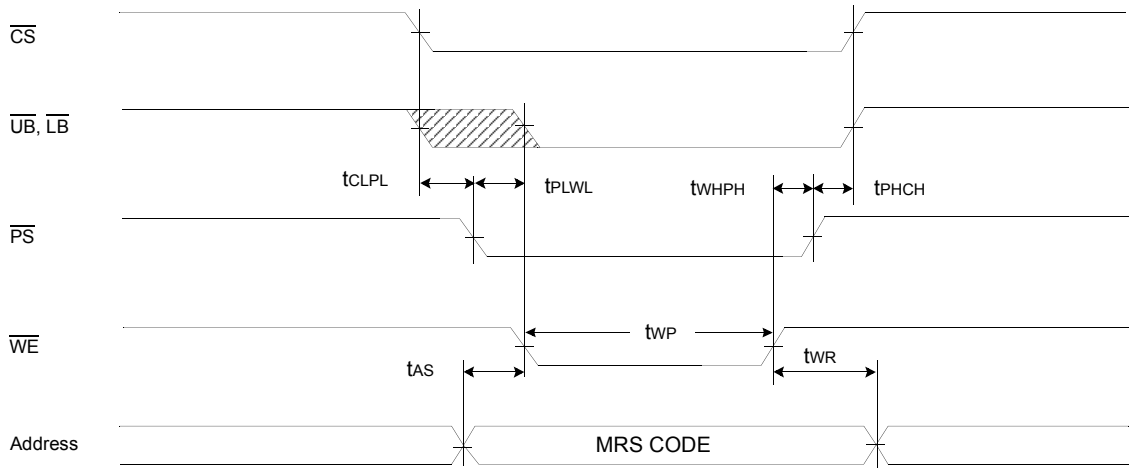
AC CHARACTERISTICS

Parameter List	Symbol	Min	Max	Units	Parameter List	Symbol	Min	Max	Units
$\overline{ADV}$ setup time to clock	t_{ADVS}	3	-	ns	Read cycle time	t_{RCM}	70	-	ns
$\overline{ADV}$ hold time from clock	t_{ADVH}	2	-	ns	$\overline{CS}$ high time	t_{CHM}	10	-	ns
Address setup time to clock	$t_{AS(B)}$	3	-	ns	$\overline{CS}$ low time	t_{CLM}	60	-	ns
Address hold time from clock	$t_{AH(B)}$	2	-	ns					

MRS TIMING WAVEFORM (PS Pin)

MRS can be implemented using by PS pin. Serial assertion of control signals of CS , UB & LB, PS and WE will get the device to be ready for MRS. MRS CODE should be set up before WE low and keep the CODE until one of those control signals desserts. MRS terminates when one of those control signals desserts. Clock & ADV are don't care in Asynchronous mode.

OE=VIH, Clock and ADV Don't care, WAIT=High-Z



AC CHARACTERISTICS

Parameter List		Symbol	Speed		Units
			Min	Max	
MRS	CS Low to PS Low	tCLPL	0	-	ns
	PS Low to WE Low	tPLWL	0	-	ns
	WE High to PS High	tWHPH	0	-	ns
	PS High to CS High	tPHCH	0	-	ns

PAR (Partial Array Refresh) mode [A3~A1]

User can select half array, a fourth array as active memory array. The active memory array is periodically refreshed(data stored), whereas the disabled array is not going to be refreshed and so the previously stored data will be invalid. When re-enabling additional portions of the array, the new portions are available immediately upon writing to the MRS.

PAR mode execution;

1) Mode Register Setting into PAR enable(A3=0)
   DPD enabled setting(A4=0) has higher priority to PAR enabled setting(A3=0). A4=1 is necessary to use PAR mode.
2) PAR mode Enter; keep $\overline{PS}$ signal at V_{IL} for longer than 0.5μs during standby mode (Mode Register: A4=1 & A3=0).
3) PAR mode Exit; The device returns to the standby mode when $\overline{PS}$ signal goes to V_{IH} during PAR mode.
   * Mode register values are not changed after the device has been to PAR mode.

DPD (Deep Power Down) mode [A4]

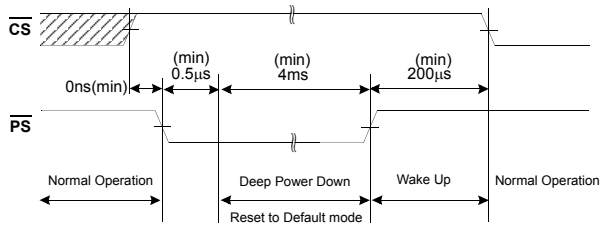
The deep power down mode disables all the refresh related activities. This mode can be used when the system needs to save power. The data become invalid when DPD mode is executed.

DPD mode execution ;

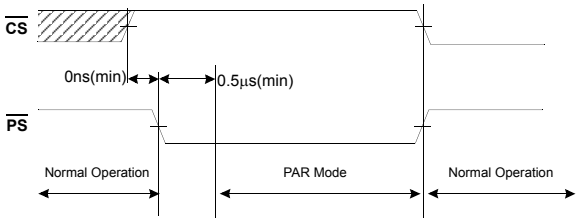
1) Mode Register Setting into DPD enable(A4=0)
2) DPD mode Enter; keep $\overline{PS}$ signal at V_{IL} for more than 0.5μs during standby mode (Mode Register: A4=0).
3) DPD mode Exit; The device returns to initial State when $\overline{PS}$ signal goes to V_{IH} during DPD mode. Wake up sequence is needed for the device to do normal operation.

Mode register values are initialized to default value after the device has been to DPD mode.
Once the device enters DPD mode, it should last over 4ms or the default mode can not be guaranteed after DPD exit.
* Default modes are Async. Read and Async. Write / DPD disable / PAR disable.

DPD MODE EXECUTION and EXIT



PAR MODE EXECUTION and EXIT



STANDBY MODE CHARACTERISTICS

Power Mode	Address (Bottom Array)[2]	Address (Top Array)[2]	Memory Cell Data	Standby[3] (I_{SB1}, <40°C)	Standby[3] (I_{SB1}, <85°C)	Wait Time(μs)
Standby(Full Array)	000000h ~ 7FFFFFh	000000h ~ 7FFFFFh	Valid[1]	TBD	TBD	0
Partial Refresh(1/2 Block)	000000h ~ 3FFFFFh	400000h ~ 7FFFFFh	Valid[1]	TBD	TBD	0
Partial Refresh(1/4 Block)	000000h ~ 1FFFFFh	600000h ~ 7FFFFFh	Valid[1]	TBD	TBD	0
Deep Power Down	000000h ~ 7FFFFFh		Invalid	TBD	TBD	200

1. Only the data in the selected block are valid
2. PAR Array can be selected through Mode Register Set
3. Standby mode is supposed to be set up after at least one active operation after power up.
   I_{SB1} is measured after 60ms from the time when standby mode is set up.

Burst Length [A7~A5] & Wrap [A12]

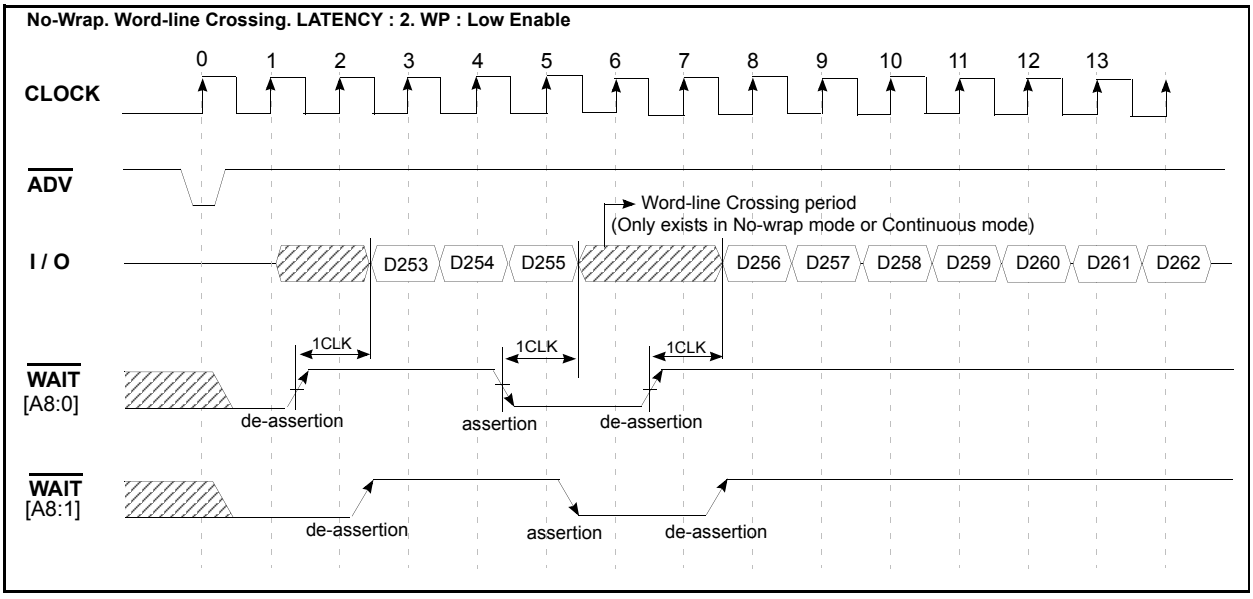
The device supports 4 word, 8 word, 16 word, 32 word and Continuous burst read or write. and Wrap & No-Wrap are supported for Burst sequence.

Burst Address Sequence(Decimal)					
Mode	**Start**	**4 word**	**8 word**	**16 word**	**32 word**
WRAP	0	0-1-2-3	0-1-2-3-4-5-6-7	0-1-2-3-4-5-6-7-8-9-10-11-12-13-14-15	0 - 1 - 2 - 3 - 4 - 5 ~ 26-27-28-29-30-31
	1	1-2-3-0	1-2-3-4-5-6-7-0	1-2-3-4-5-6-7-8-9-10-11-12-13-14-15-0	1 - 2 - 3 - 4 - 5 - 6 ~ 27-28-29-30-31 - 0
	2	2-3-0-1	2-3-4-5-6-7-0-1	2-3-4-5-6-7-8-9-10-11-12-13-14-15-0-1	2 - 3 - 4 - 5 - 6 - 7 ~ 28-29-30-31 - 0 - 1
	3	3-0-1-2	3-4-5-6-7-0-1-2	3-4-5-6-7-8-9-10-11-12-13-14-15-0-1-2	3 - 4 - 5 - 6 - 7 - 8 ~ 29-30-31- 0 - 1 - 2
	~		~	~	~
	7		7-0-1-2-3-4-5-6	7-8-9-10-11-12-13-14-15-0-1-2-3-4-5-6	7 - 8 - 9 - 10- 11- 12 ~ 2 - 3 - 4 - 5 - 6
	~			~	~
	15			15-0-1-2-3-4-5-6-7-8-9-10-11-12-13-14	15-16-17-18-19-20 ~ 10- 11- 12- 13- 14
	~				~
	31				31- 0 - 1 - 2 - 3 - 4 ~ 25-26-27-28-29-30
No-WRAP	0	0-1-2-3	0- 1- 2- 3- 4- 5- 6 -7	0- 1- 2- 3- 4- 5- 6- 7- 8- 9- 10- 11- 12-13-14-15	0 - 1 - 2 - 3 - 4 - 5 ~ 26-27-28-29-30-31
	1	1-2-3-4	1- 2- 3- 4- 5- 6- 7- 8	1- 2- 3- 4- 5- 6- 7- 8- 9- 10- 11- 12-13-14-15-16	1 - 2 - 3 - 4 - 5 - 6 ~ 27-28-29-30-31-32
	2	2-3-4-5	2- 3- 4- 5- 6- 7- 8- 9	2- 3- 4- 5- 6- 7- 8- 9- 10- 11- 12-13-14-15-16-17	2 - 3 - 4 - 5 - 6 - 7 ~ 28-29-30-31-32-33
	3	3-4-5-6	3- 4- 5- 6- 7- 8- 9-10	3- 4- 5- 6- 7- 8- 9- 10- 11- 12-13-14-15-16-17-18	3 - 4 - 5 - 6 - 7 - 8 ~ 29-30-31-32-33-34
	~		~	~	~
	7		7-8-9-10-11-12-13-14	7-8-9-10-11-12-13-14-15-16-17-18-19-20-21-22	7 - 8 - 9 - 10-11-12 ~ 33-34-35-36-37-38
	~			~	~
	15			15-16-17-18-19-20-21-22-23-24-25-26-27-28-29-30	15-16-17-18-19-20 ~ 41-42-43-44-45-46
	~				~
	31				31-32-33-34-35-36 ~ 57-58-59-60-61-62

1. Continuous Burst mode needs to meet tBC(max. 1.2us) parameter.

$\overline{\text{WAIT}}$ Configuration [A8] & $\overline{\text{WAIT}}$ Polarity [A13]

The $\overline{\text{WAIT}}$ signal is output signal indicating the status of the data on the bus whether or not it is valid. $\overline{\text{WAIT}}$ configuration is to decide the timing when $\overline{\text{WAIT}}$ asserts or desserts. $\overline{\text{WAIT}}$ asserts (or desserts) one clock prior to the data when A8 is set to 0. ($\overline{\text{WAIT}}$ asserts (or desserts) at data clock when A8 is set to 1). $\overline{\text{WAIT}}$ polarity is to decide the $\overline{\text{WAIT}}$ signal level at which data is valid or invalid. Data is valid if $\overline{\text{WAIT}}$ signal is high when A13 is set to 0. (Data is valid if $\overline{\text{WAIT}}$ signal is low when A13 is set to 1). All the timing diagrams in this SPEC are illustrated based on following setup; [A13 : 0] and [A8 : 0].
Below timing shows $\overline{\text{WAIT}}$ signal's movement when word boundary crossing happens in No-wrap mode.

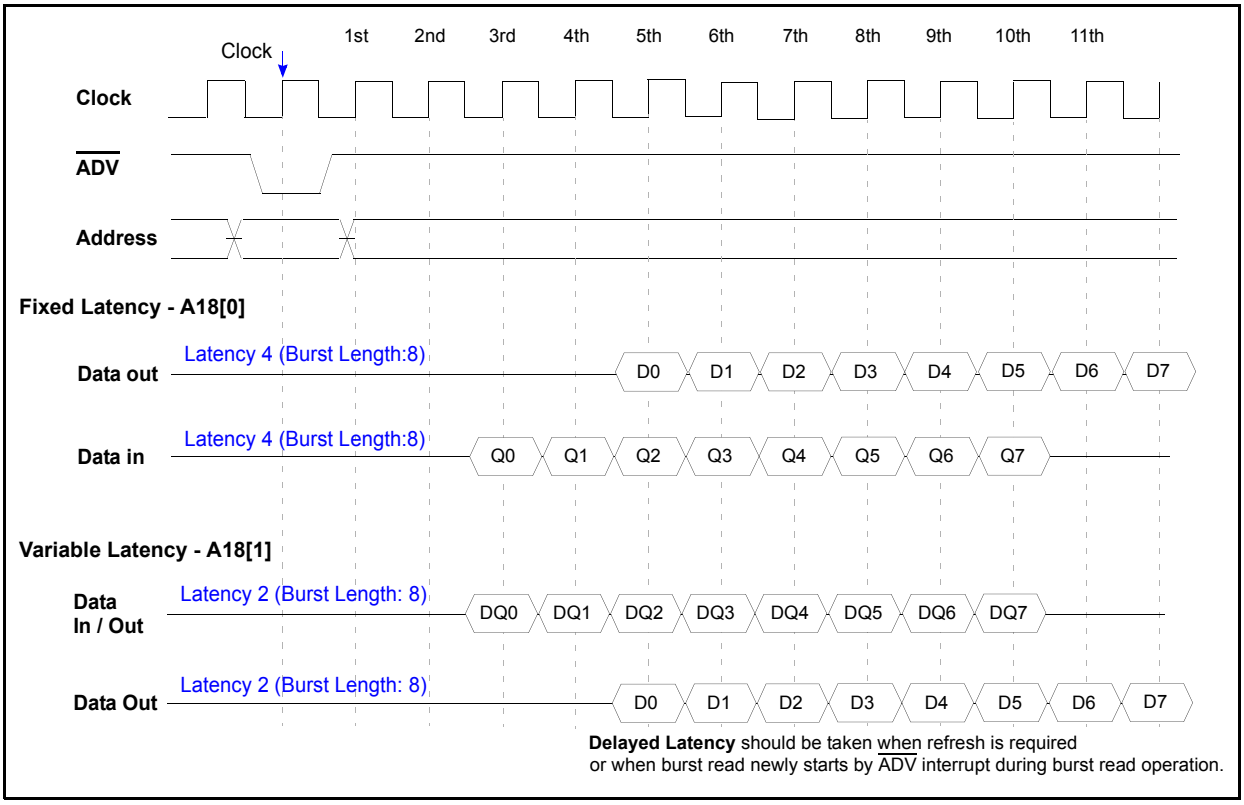


Latency [A11~A9]

The Latency stands for the number of clocks before the first data available from the burst command.

Item	Upto 66MHz		Upto 80MHz		Upto 104MHz	
	Fixed	Variable	Fixed	Variable	Fixed	Variable
Latency Set(A11:A10:A9)	4(0:0:1)	2(1:0:0)	5(0:1:0)	3(0:0:0)	7(1:0:1)	4(0:0:1)
Read Latency(min)	4	2 / 4[1)]	5	3 / 5[1)]	7	4 / 7[1)]
1st Read data fetch clock	5th	3rd / 5th[1)]	6th	4th / 6th[1)]	8th	5th / 8th[1)]
Write Latency(min)	2	2	3	3	4	4
1st Write data loading clock	3rd	3rd	4th	4th	5th	5th

1) **Delayed Latency** should be taken when refresh is required or when burst read newly starts by $\overline{ADV}$ interrupt during burst read operation.



Driver Strength [A17~A16]

The optimization of output driver strength is possible to adjust for the different data loadings. The device can minimize the noise generated on the data bus during read operation. The device supports full, 1/2 and 1/4 driver strength. The device's default mode is 1/2 driver strength.

Driver Strength	Full	1 / 2	1 / 4
IMPEDANCE(typ.)	40Ω	90Ω	150Ω

1. Impedance values are typical values, not 100% tested.

OPEARTION MODE [A15~A14]

MODE1. ASYNCHRONOUS READ / ASYNCHRONOUS WRITE MODE

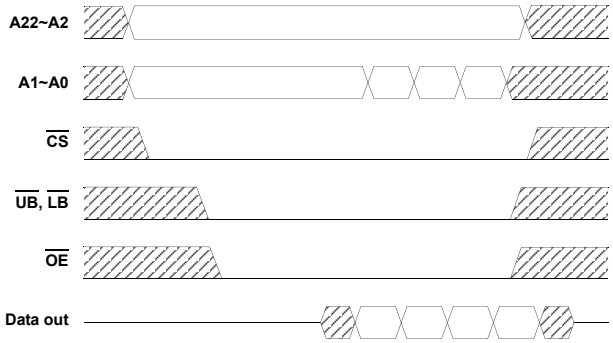
Asynchronous read operation

Asynchronous read operation starts when $\overline{CS}$, $\overline{OE}$ and $\overline{UB}$ or $\overline{LB}$ are asserted. First data come out after random access time(tAA) but second, third and fourth data come out after page access time(tPA) when using the page addresses (A0, A1). $\overline{PS}$ and $\overline{WE}$ should be de-asserted during read operation. Clock, $\overline{ADV}$ are don't care during read operation and $\overline{WAIT}$ is Hi-Z.

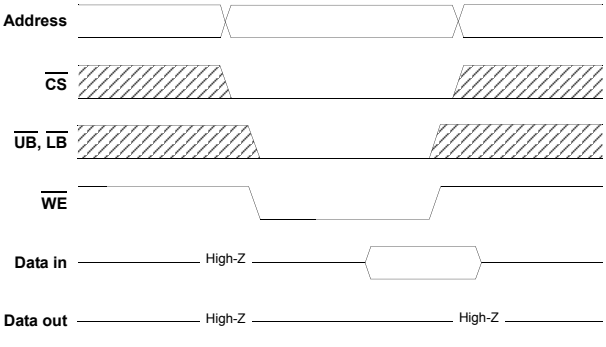
Asynchronous write operation

Asynchronous write operation starts when $\overline{CS}$, $\overline{WE}$ and $\overline{UB}$ or $\overline{LB}$ are asserted. $\overline{PS}$ and should be de-asserted during write operation. Clock, $\overline{OE}$, $\overline{ADV}$ are don't care during write operation and $\overline{WAIT}$ signal is Hi-Z.

ASYNCHRONOUS 4-PAGE READ



ASYNCHRONOUS WRITE



FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{PS}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	I/O0~7	I/O8~15	Mode	Power
H	H	X[1)]	X[1)]	X[1)]	X[1)]	High-Z	High-Z	Deselected	Standby
H	L	X[1)]	X[1)]	X[1)]	X[1)]	High-Z	High-Z	Deselected	DPD or PAR
L	H	H	H	X[1)]	X[1)]	High-Z	High-Z	Output Disabled	Active
L	H	X[1)]	X[1)]	H	H	High-Z	High-Z	Output Disabled	Active
L	H	L	H	L	H	Dout	High-Z	Lower Byte Read	Active
L	H	L	H	H	L	High-Z	Dout	Upper Byte Read	Active
L	H	L	H	L	L	Dout	Dout	Word Read	Active
L	H	H	L	L	H	Din	High-Z	Lower Byte Write	Active
L	H	H	L	H	L	High-Z	Din	Upper Byte Write	Active
L	H	H	L	L	L	Din	Din	Word Write	Active

1. X means "Don't care". X should be low or high state.
2. In asynchronous mode, Clock and $\overline{ADV}$ are ignored. Clock and $\overline{ADV}$ should be low or high state.
3. /WAIT pin is High-Z in Asynchronous mode.

MODE2. SYNCHRONOUS BURST READ / ASYNCHRONOUS WRITE MODE

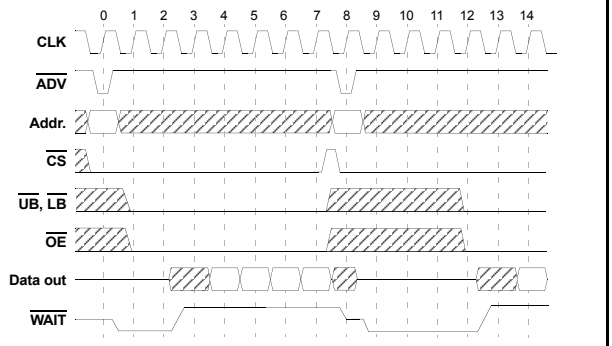
Synchronous Burst Read Operation

Burst Read command is implemented when $\overline{ADV}$ is detected low at clock rising edge. $\overline{WE}$ should be de-asserted during Burst read, Burst operation re-starts whenever $\overline{ADV}$ is detected low at clock rising edge even in the middle of operation.
Variable latency allows the UtRAM to be configured for minimum latency at high frequencies, but the controller must monitor $\overline{WAIT}$ to detect any conflict with refresh cycles.

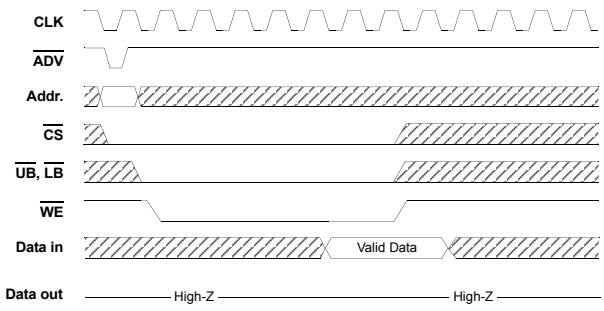
Asynchronous Write Operation

Asynchronous write operation starts when $\overline{CS}$, $\overline{WE}$ and $\overline{UB}$ or $\overline{LB}$ are asserted. $\overline{PS}$ and should be de-asserted during write operation. Clock, $\overline{OE}$, $\overline{ADV}$ are don't care during write operation and $\overline{WAIT}$ signal is Hi-Z.

SYNCHRONOUS BURST READ
(Latency 3, BL 4, WP : Low Enable, $\overline{PS}$ High, $\overline{WE}$ High)



ASYNCHRONOUS WRITE
($\overline{PS}$ High, $\overline{OE}$ High, $\overline{WAIT}$ High-Z, Clock Don't care)



FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{PS}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	I/O0~7	I/O8~15	CLK	$\overline{ADV}$	Mode	Power
H	H	X[1]	X[1]	X[1]	X[1]	High-Z	High-Z	X[1]	X[1]	Deselected	Standby
H	L	X[1]	X[1]	X[1]	X[1]	High-Z	High-Z	X[1]	X[1]	Deselected	PAR
L	H	H	H	X[1]	X[1]	High-Z	High-Z	X[1]	H	Output Disabled	Active
L	H	X[1]	X[1]	H	H	High-Z	High-Z	X[1]	H	Output Disabled	Active
L	H	X[1]	H	X[1]	X[1]	High-Z	High-Z	⌐	⌐¬⌐	Read Command	Active
L	H	L	H	L	H	Dout	High-Z	⌐	H	Lower Byte Read	Active
L	H	L	H	H	L	High-Z	Dout	⌐	H	Upper Byte Read	Active
L	H	L	H	L	L	Dout	Dout	⌐	H	Word Read	Active
L	H	H	L	L	H	Din	High-Z	X[1]	⌐ or ⌐¬⌐	Lower Byte Write	Active
L	H	H	L	H	L	High-Z	Din	X[1]	⌐ or ⌐¬⌐	Upper Byte Write	Active
L	H	H	L	L	L	Din	Din	X[1]	⌐ or ⌐¬⌐	Word Write	Active

1. X means "Don't care". X should be low or high state.
2. /WAIT is device output signal so does not have any affect to the mode definition. Please refer to each timing diagram for /WAIT pin function.

MODE3. SYNCHRONOUS BURST READ / SYNCHRONOUS BURST WRITE MODE

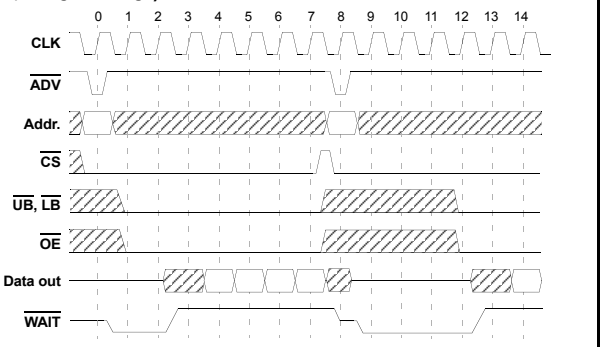
Synchronous Burst Read Operation

Burst Read command is implemented when $\overline{ADV}$ is detected low at clock rising edge. $\overline{WE}$ should be de-asserted during Burst read, Burst Read operation re-starts whenever $\overline{ADV}$ is detected low at clock rising edge even in the middle of Burst Read operation. Variable latency allows the UtRAM to be configured for minimum latency at high frequencies, but the controller must monitor $\overline{WAIT}$ to detect any conflict with refresh cycles.

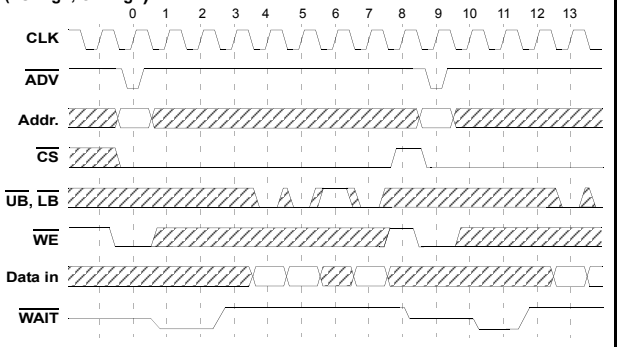
Synchronous Burst Write Operation

Burst Write command is implemented when $\overline{ADV}$ & $\overline{WE}$ are detected low at clock rising edge. Burst Write operation re-starts whenever $\overline{ADV}$ is detected low at clock rising edge even in the middle of Burst Write operation.
Write operations always use fixed latency.

SYNCHRONOUS BURST READ(Latency 3, BL 4, WP : Low Enable)
($\overline{PS}$ High, $\overline{WE}$ High)



SYNCHRONOUS BURST WRITE(Latency 3, BL 4, WP : Low Enable)
($\overline{PS}$ High, $\overline{OE}$ High)



FUNCTIONAL DESCRIPTION

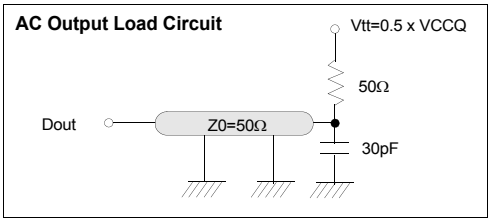
$\overline{CS}$	$\overline{PS}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	I/O0~7	I/O8~15	CLK	$\overline{ADV}$	Mode	Power
H	H	X[1]	X[1]	X[1]	X[1]	High-Z	High-Z	X[1]	X[1]	Deselected	Standby
H	L	X[1]	X[1]	X[1]	X[1]	High-Z	High-Z	X[1]	X[1]	Deselected	PAR
L	H	H	H	X[1]	X[1]	High-Z	High-Z	X[1]	H	Output Disabled	Active
L	H	X[1]	X[1]	H	H	High-Z	High-Z	X[1]	H	Output Disabled	Active
L	H	X[1]	H	X[1]	X[1]	High-Z	High-Z	⌐¯	⌐¯¬	Read Command	Active
L	H	L	H	L	H	Dout	High-Z	⌐¯	H	Lower Byte Read	Active
L	H	L	H	H	L	High-Z	Dout	⌐¯	H	Upper Byte Read	Active
L	H	L	H	L	L	Dout	Dout	⌐¯	H	Word Read	Active
L	H	X[1]	L	X[1]	X[1]	High-Z	High-Z	⌐¯	⌐¯¬	Write Command	Active
L	H	H	X[1]	L	H	Din	High-Z	⌐¯	H	Lower Byte Write	Active
L	H	H	X[1]	H	L	High-Z	Din	⌐¯	H	Upper Byte Write	Active
L	H	H	X[1]	L	L	Din	Din	⌐¯	H	Word Write	Active
L	L	H	L	L	L	High-Z	High-Z	⌐¯	⌐¯¬	Mode Register Set	Active

1. X means "Don't care". X should be low or high state.
2. /WAIT is device output signal so does not have any affect to the mode definition. Please refer to each timing diagram for /WAIT pin function.

MODE 1 AC OPERATING CONDITIONS (ASYNCH. READ / ASYNCH. WRITE)

TEST CONDITIONS

(Test Load and Test Input/Output Reference)
Input pulse level: 0.2 to V_{CCQ}-0.2V
Input rising and falling time: 3ns
Input and output reference voltage: 0.5 x V_{CCQ}
Output load: C_L=30pF
V_{CC}:1.7V~1.95V
T_A: -40°C~85°C



AC CHARACTERISTICS

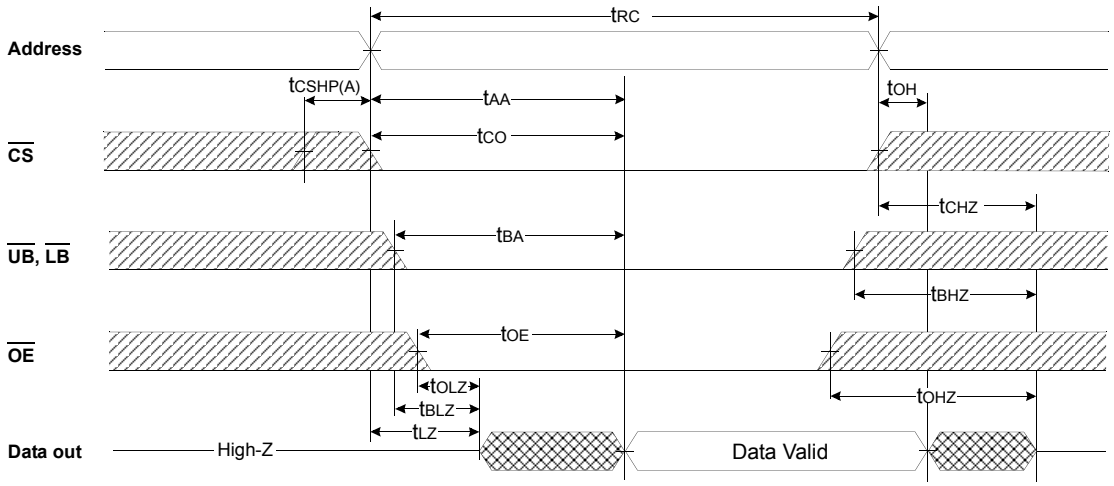
Parameter List		Symbol	Speed		Units
			Min	Max	
Common	$\overline{CS}$ High Pulse Width	$t_{CSHP(A)}$	10	-	ns
Asynch. Read	Read Cycle Time	t_{RC}	70	-	ns
	Page Read Cycle Time	t_{PC}	20	-	ns
	Address Access Time	t_{AA}	-	70	ns
	Page Access Time	t_{PA}	-	20	ns
	Chip Select to Output	t_{CO}	-	70	ns
	Output Enable to Valid Output	t_{OE}	-	20	ns
	$\overline{UB}$, $\overline{LB}$ Access Time	t_{BA}	-	20	ns
	Chip Select to Low-Z Output	t_{LZ}	10	-	ns
	$\overline{UB}$, $\overline{LB}$ Enable to Low-Z Output	t_{BLZ}	5	-	ns
	Output Enable to Low-Z Output	t_{OLZ}	5	-	ns
	Chip Disable to High-Z Output	t_{CHZ}	0	10	ns
	$\overline{UB}$, $\overline{LB}$ Disable to High-Z Output	t_{BHZ}	0	10	ns
	Output Disable to High-Z Output	t_{OHZ}	0	10	ns
	Output Hold	t_{OH}	5	-	ns
Asynch. Write	Write Cycle Time	t_{WC}	70	-	ns
	Chip Select to End of Write	t_{CW}	60	-	ns
	Address Set-up Time to Beginning of Write	t_{AS}	0	-	ns
	Address Valid to End of Write	t_{AW}	60	-	ns
	$\overline{UB}$, $\overline{LB}$ Valid to End of Write	t_{BW}	60	-	ns
	Write Pulse Width	t_{WP}	55[1)]	-	ns
	$\overline{WE}$ High Pulse Width	t_{WHP}	5	-	ns
	Write Recovery Time	t_{WR}	0	-	ns
	Data to Write Time Overlap	t_{DW}	20	-	ns
	Data Hold from Write Time	t_{DH}	0	-	ns

1. t_{WP}(min)=70ns for continuous write without CS toggling longer than 1.2us
2. The High-Z timings measure a 100mV transition from either V_{OH} or V_{OL} toward V_{CCQ} x 0.5
3. The Low-Z timings measure a 100mV transition away from the High-Z level toward either V_{OH} or V_{OL}.

TIMING WAVEFORMS (ASYNCH. READ / ASYNCH. WRITE)

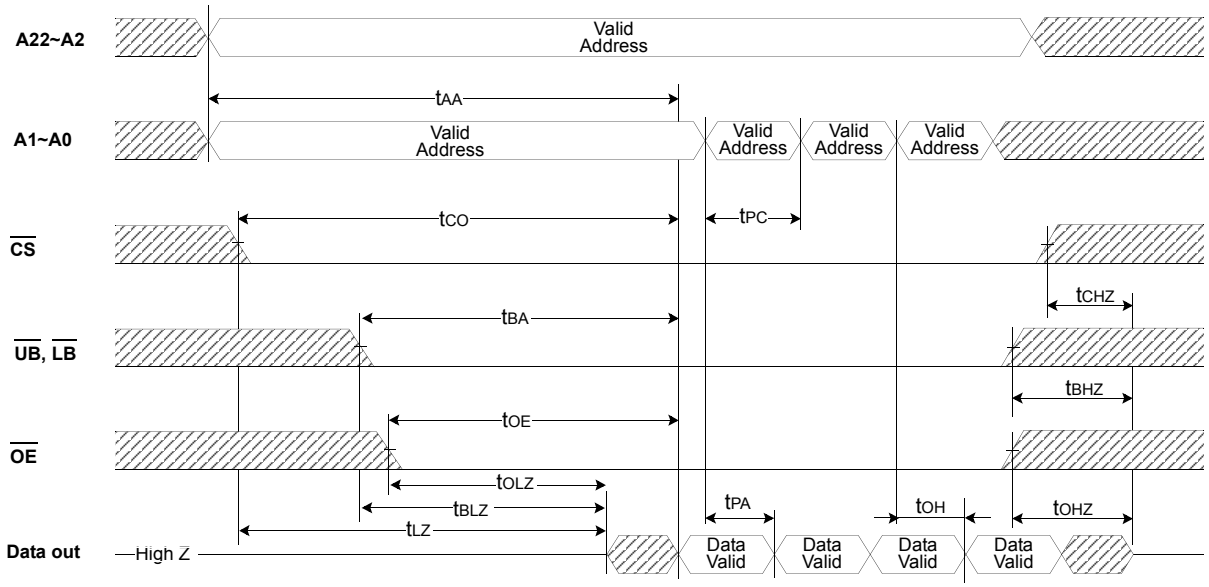
Asynch. READ

($\overline{PS}$=VIH, $\overline{WE}$=VIH, $\overline{WAIT}$=High-Z)



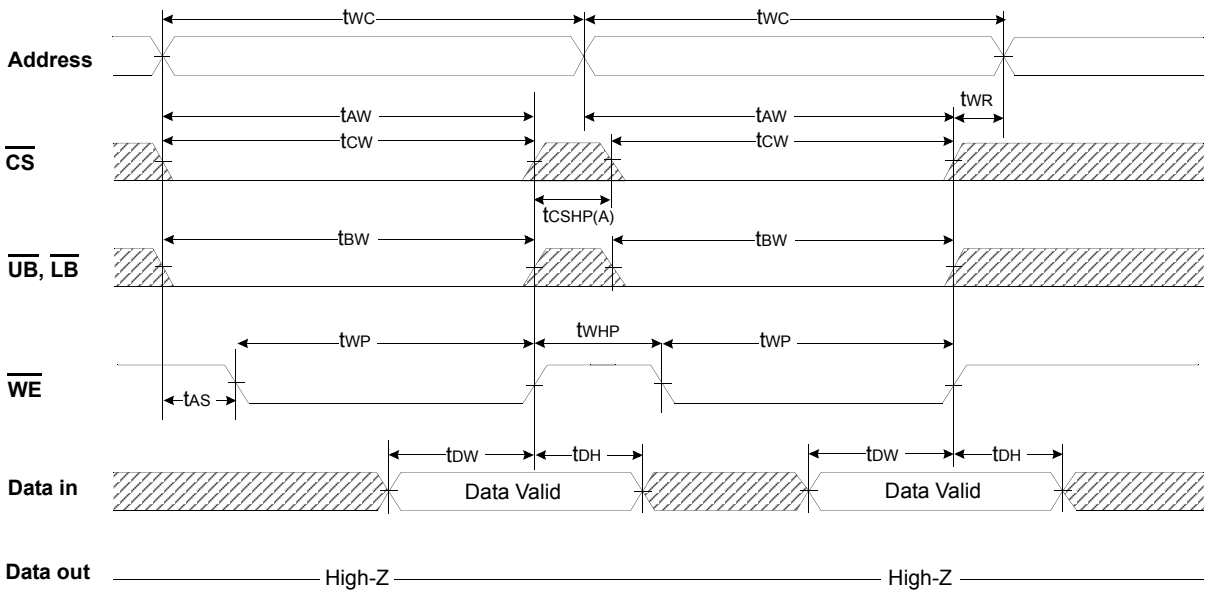
Asynch. PAGE READ

($\overline{PS}$=VIH, $\overline{WE}$=VIH, $\overline{WAIT}$=High-Z)

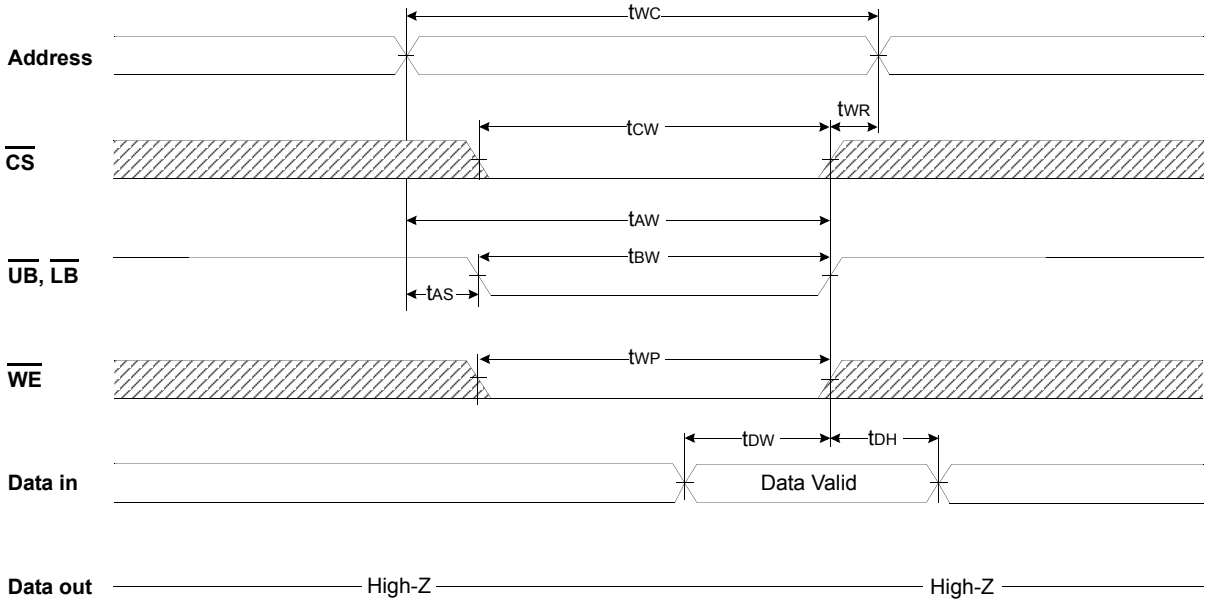


1. tCHZ and tOHZ are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, tCHZ(Max.) is less than tLZ(Min.) both for a given device and from device to device interconnection.
3. In asynchronous read cycle, Clock and $\overline{ADV}$ signals are ignored.
4. If invalid address signals shorter than min. tRC are continuously repeated for over 1.2us, the device needs a normal read timing(tRC) or needs to sustain standby state for min. tRC at least once in every 1.2us.
5. In asynchronous 4 page read cycle, Clock and $\overline{ADV}$ signals are ignored.

Asynch. WRITE (1)
(PS=VIH, OE=VIH, WAIT=High-Z, WE Controlled)



Asynch. WRITE (2)
(PS=VIH, OE=VIH, WAIT=High-Z, UB & LB Controlled)

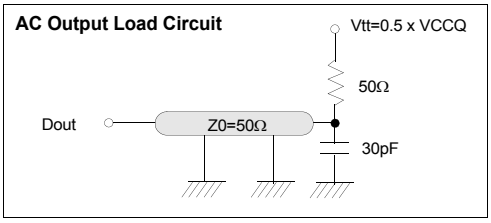


1. A write occurs during the overlap(tWP) of low CS and low WE. A write begins when CS goes low and WE goes low with asserting UB or LB for single byte operation or simultaneously asserting UB and LB for double byte operation. A write ends at the earliest transition when CS goes high or WE goes high. The tWP is measured from the beginning of write to the end of write.
2. tCW is measured from the CS going low to the end of write.
3. tAS is measured from the address valid to the beginning of write.
4. tWR is measured from the end of write to the address change. tWR is applied in case a write ends with CS or WE going high.
5. In asynchronous write cycle, Clock and ADV signals are ignored.
6. Condition for continuous write operation over 15 times : tWP(min)=70ns

MODE 2 AC OPERATING CONDITIONS (SYNCH. READ / ASYNCH. WRITE)

TEST CONDITIONS

(Test Load and Test Input/Output Reference)
Input pulse level: 0.2 to V_{CCQ}-0.2V
Input rising and falling time: 1ns
Input and output reference voltage: 0.5 x V_{CCQ}
Output load: C_L=30pF
V_{CC}:1.7V~1.95V
T_A: -40°C~85°C



AC CHARACTERISTICS

Parameter List		Symbol	66MHz		80MHz		104MHz		Units
			Min	Max	Min	Max	Min	Max	
Synch. Burst Read	Clock Cycle Time	T	15	200	12.5	200	9.6	200	ns
	Burst Cycle Time	t_{BC}	-	1200	-	1200	-	1200	ns
	Address Set-up Time to clock	$t_{AS(B)}$	3	-	3	-	3	-	ns
	Address Hold Time from clock	$t_{AH(B)}$	2	-	2	-	2	-	ns
	$\overline{ADV}$ Setup Time to clock	t_{ADVS}	3	-	3	-	3	-	ns
	$\overline{ADV}$ Hold Time from clock	t_{ADVH}	2	-	2	-	2	-	ns
	$\overline{CS}$ Setup Time to clock	$t_{CSS(B)}$	3	-	3	-	3	-	ns
	$\overline{CS}$ High to $\overline{ADV}$ Low (Burst Stop)	t_{BSADV}[1]	0		0		0		ns
	$\overline{CS}$ Low Hold Time from Clock(Burst Stop)	t_{CSLH}	2	-	2	-	2	-	ns
	$\overline{CS}$ High Pulse Width	t_{CSHP}	5	-	5	-	5	-	ns
	$\overline{CS}$ Low to $\overline{WAIT}$ Low	t_{WL}	-	12	-	12	-	12	ns
	Clock to $\overline{WAIT}$ High	t_{WH}	-	11	-	9	-	7	ns
	$\overline{CS}$ High to $\overline{WAIT}$ High-Z	t_{WZ}	-	10	-	10	-	10	ns
	$\overline{UB}$, $\overline{LB}$ Low to End of Latency Clock	t_{BEL}	20	-	20	-	20	-	ns
	$\overline{OE}$ Low to End of Latency Clock	t_{OEL}	20	-	20	-	20	-	ns
	$\overline{UB}$, $\overline{LB}$ Low to Low-Z Output	t_{BLZ}	5	-	5	-	5	-	ns
	$\overline{OE}$ Low to Low-Z Output	t_{OLZ}	5	-	5	-	5	-	ns
	Clock Rising to Data Output	t_{CD}	-	11	-	9	-	7	ns
	Output Hold from clock	$t_{OH(B)}$	2	-	2	-	2	-	ns
	Burst End Clock to Output High-Z	t_{HZ}	-	10	-	10	-	10	ns
	$\overline{CS}$ High to Output High-Z	t_{CHZ}	-	10	-	10	-	10	ns
	$\overline{OE}$ High to Output High-Z	t_{OHZ}	-	10	-	10	-	10	ns
	$\overline{UB}$, $\overline{LB}$ High to Output High-Z	t_{BHZ}	-	10	-	10	-	10	ns

1. Refresh can not be implemented when tBSADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.2us without $\overline{CS}$ toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBSADV.
2. The High-Z timings measure a 100mV transition from either V_{OH} or V_{OL} toward V_{CCQ} x 0.5
3. The Low-Z timings measure a 100mV transition away from the High-Z level toward either V_{OH} or V_{OL}.

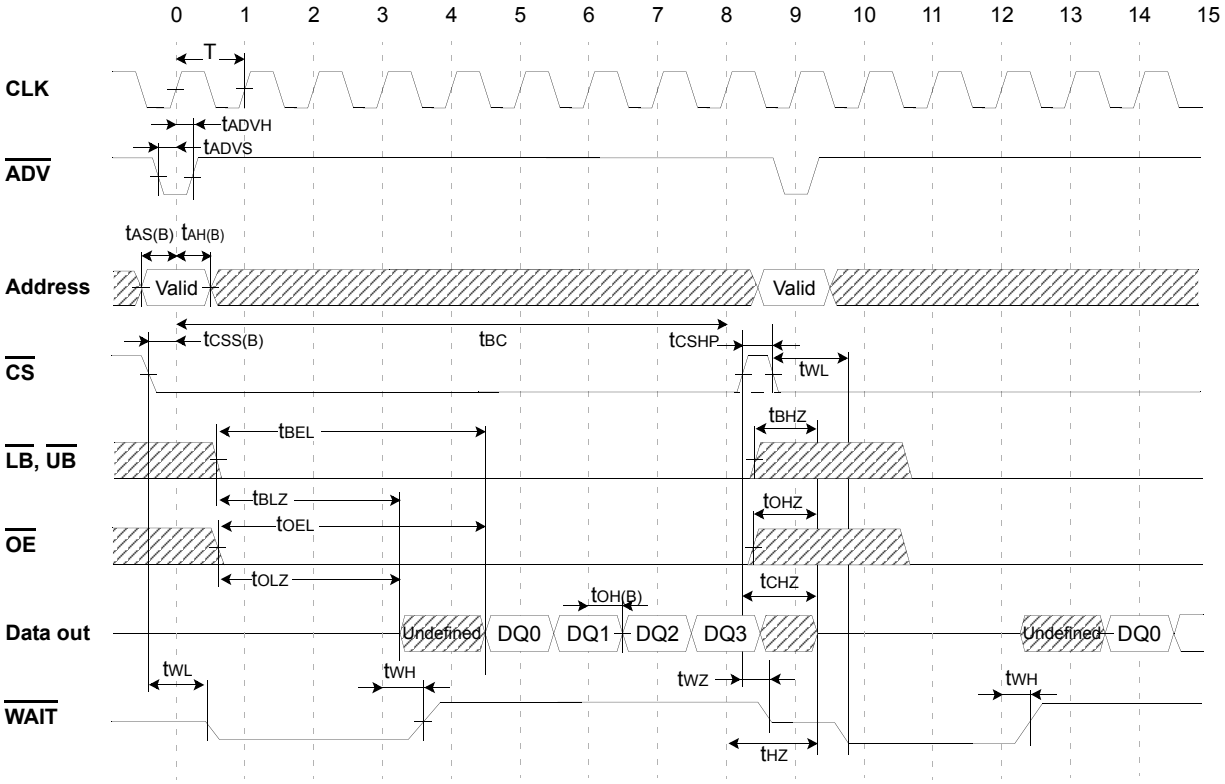
Parameter List		Symbol	Speed		Units
			Min	Max	
Asynch. Write	Write Cycle Time	t_{WC}	70	-	
	Chip Select to End of Write	t_{CW}	60	-	ns
	$\overline{ADV}$ Minimum Low Pulse Width	t_{ADV}	5	-	ns
	Address Set-up Time to Beginning of Write	t_{AS}	0	-	ns
	Address Set-up Time to $\overline{ADV}$ Rising	$t_{AS(A)}$	5	-	ns
	Address Hold Time from $\overline{ADV}$ Rising	$t_{AH(A)}$	3	-	ns
	$\overline{CS}$ Setup Time to $\overline{ADV}$ Rising	$t_{CSS(A)}$	5	-	ns
	Address Valid to End of Write	t_{AW}	60	-	ns
	$\overline{UB}$, $\overline{LB}$ Valid to End of Write	t_{BW}	60	-	ns
	Write Pulse Width	t_{WP}	55[1]	-	ns
	Write Recovery Time	t_{WR}	0	-	ns
	Data to Write Time Overlap	t_{DW}	20	-	ns
	Data Hold from Write Time	t_{DH}	0	-	ns

1. t_{WP}(min)=70ns for continuous write longer than 1.2us without $\overline{CS}$ toggling.

TIMING WAVEFORMS (SYNCH. READ / ASYNCH. WRITE)

Burst READ - Fixed Latency

($\overline{PS}$=VIH, $\overline{WE}$=VIH, $\overline{WAIT}$=High-Z, Latency=4, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



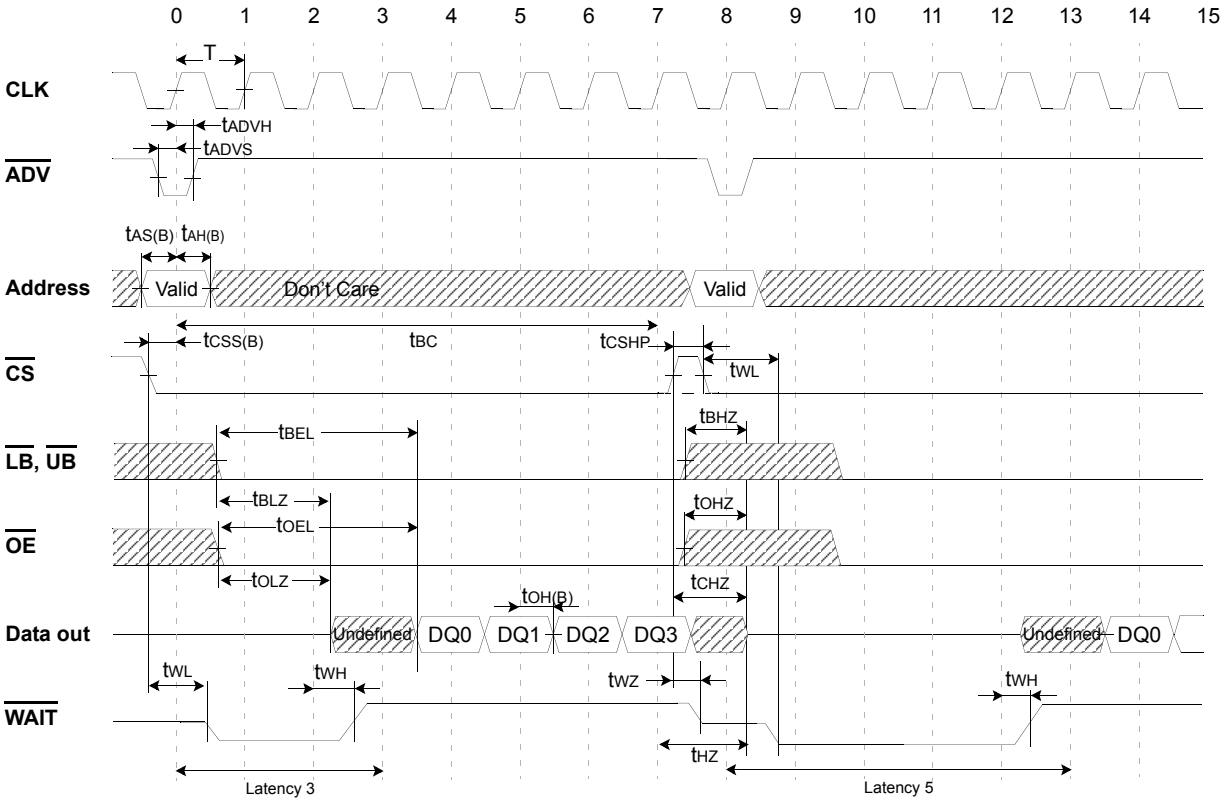
1. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
2. Multiple clock risings are allowed during low $\overline{ADV}$ period. The data starts after set Latency from the last clock rising.
3. Burst operation should not be longer than tBC(1.2μs)

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1200	-	1200	-	1200	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

Burst READ - Variable Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=3,Burst Length=4, WP=Low enable, WC=one clock prior to the data)



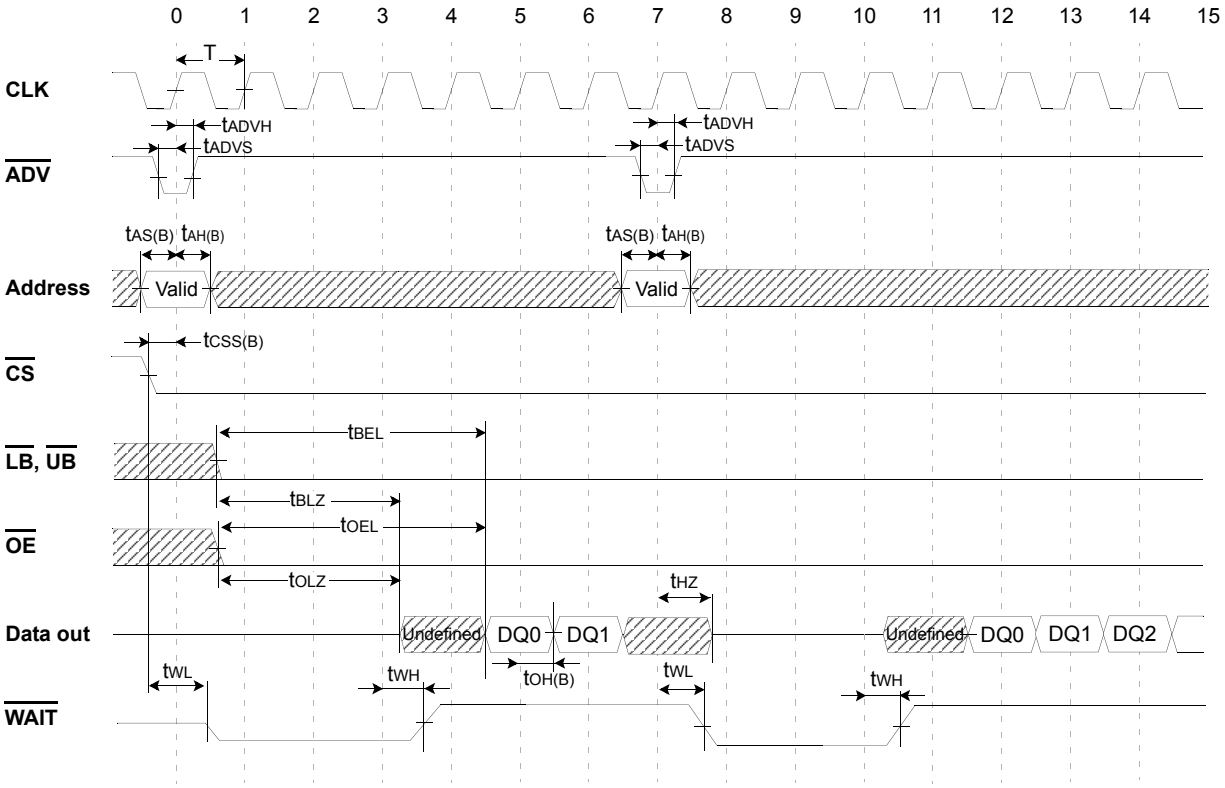
1. Delayed Latency should be taken increased when refresh is required. Refer to Latency Table.
2. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
3. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
4. Burst operation should not be longer than tBC(1.2μs)

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1200	-	1200	-	1200	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

Burst READ ($\overline{ADV}$ Interrupt) - Fixed Latency

($\overline{PS}$=VIH, $\overline{WE}$=VIH, $\overline{WAIT}$=High-Z, Latency=4, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



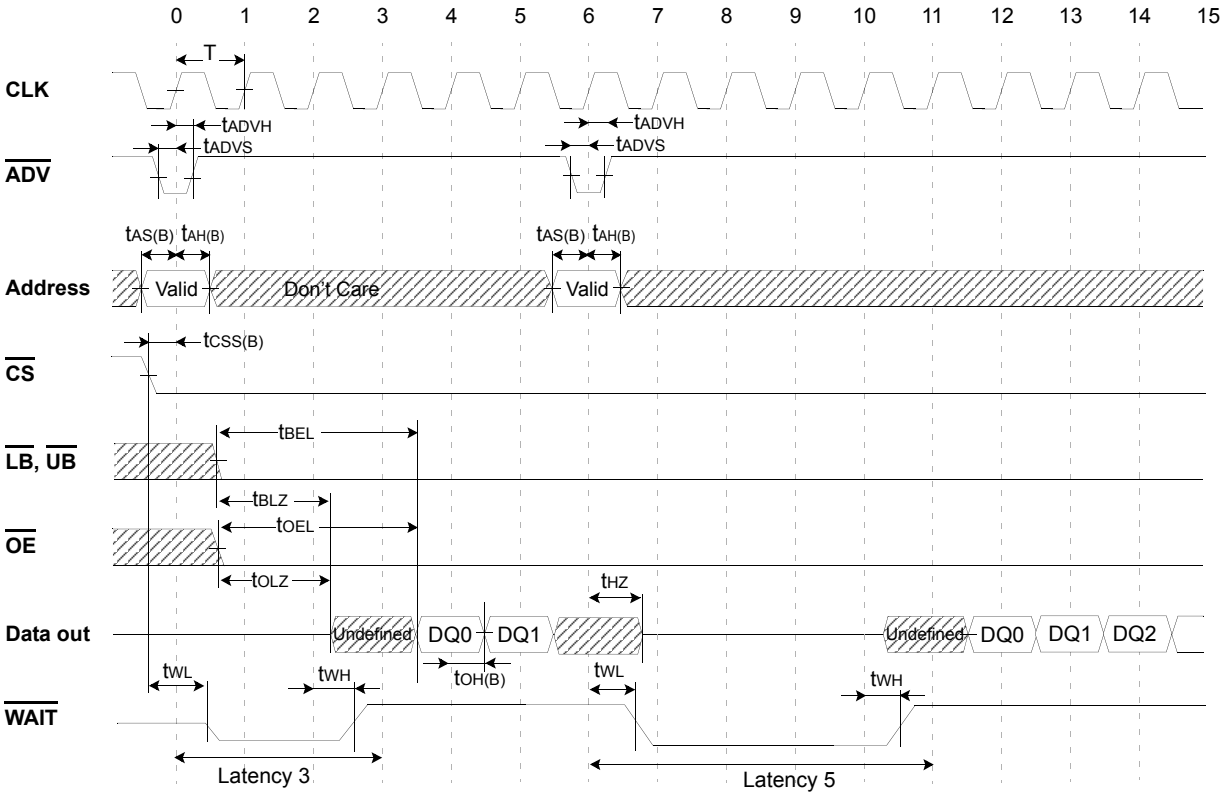
1. Refresh is blocked during $\overline{ADV}$ Interrupt Read and continuous Burst Read by ADV interrupt should not be longer than tBC (1.2us)
2. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
3. Multiple clock risings are allowed during low $\overline{ADV}$ period but the First valid data come out after set Latency from the last clock rising.
4. Burst interrupt is allowable after the first data received by controller.

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1200	-	1200	-	1200	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

Burst READ ($\overline{ADV}$ Interrupt) - Variable Latency

($\overline{PS}$=VIH, $\overline{WE}$=VIH, $\overline{WAIT}$=High-Z, Latency=3, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



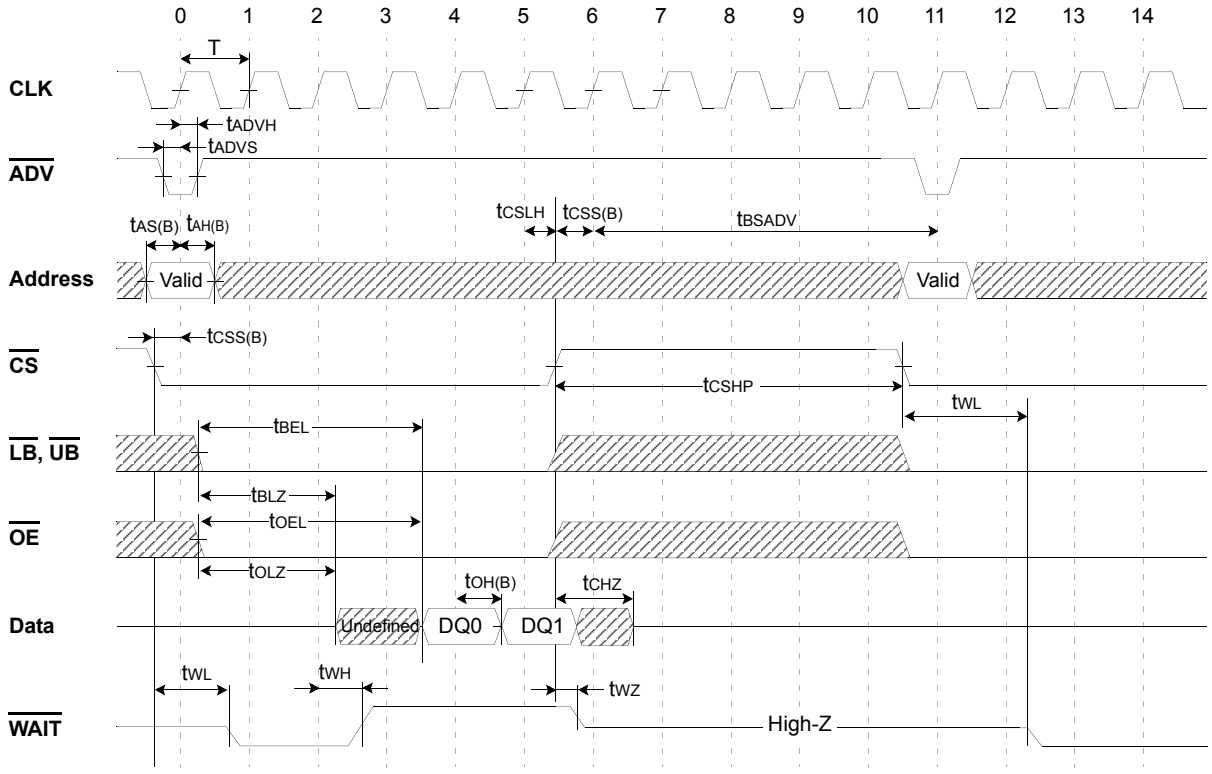
1. Delayed Latency should be taken increased when refresh is required. Refer to Latency Table.
2. Refresh is blocked during $\overline{ADV}$ Interrupt Read and continuous Burst Read by ADV interrupt should not be longer than tBC (1.2us)
3. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
4. Multiple clock risings are allowed during low $\overline{ADV}$ period but the First valid data come out after set Latency from the last clock rising.
5. Burst interrupt is allowable after the first data received by controller.

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1200	-	1200	-	1200	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

Burst READ STOP

(PS=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)

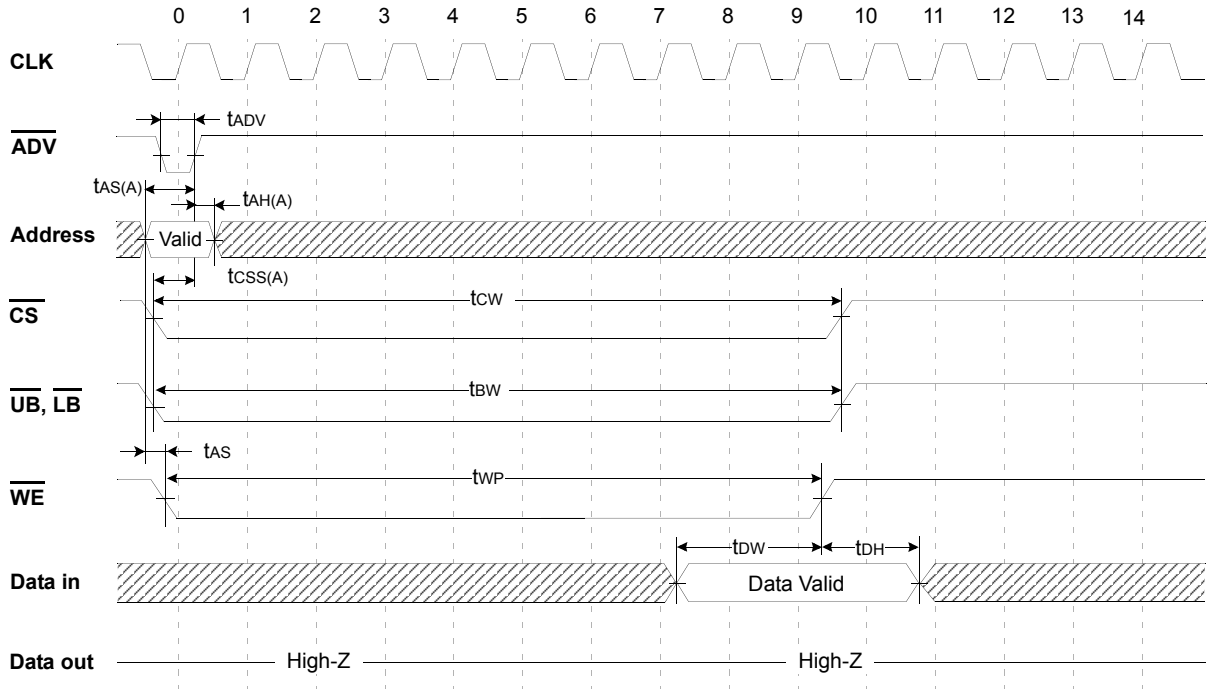


1. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
2. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
3. Refresh can not be implemented when tBSADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.2us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBSADV.

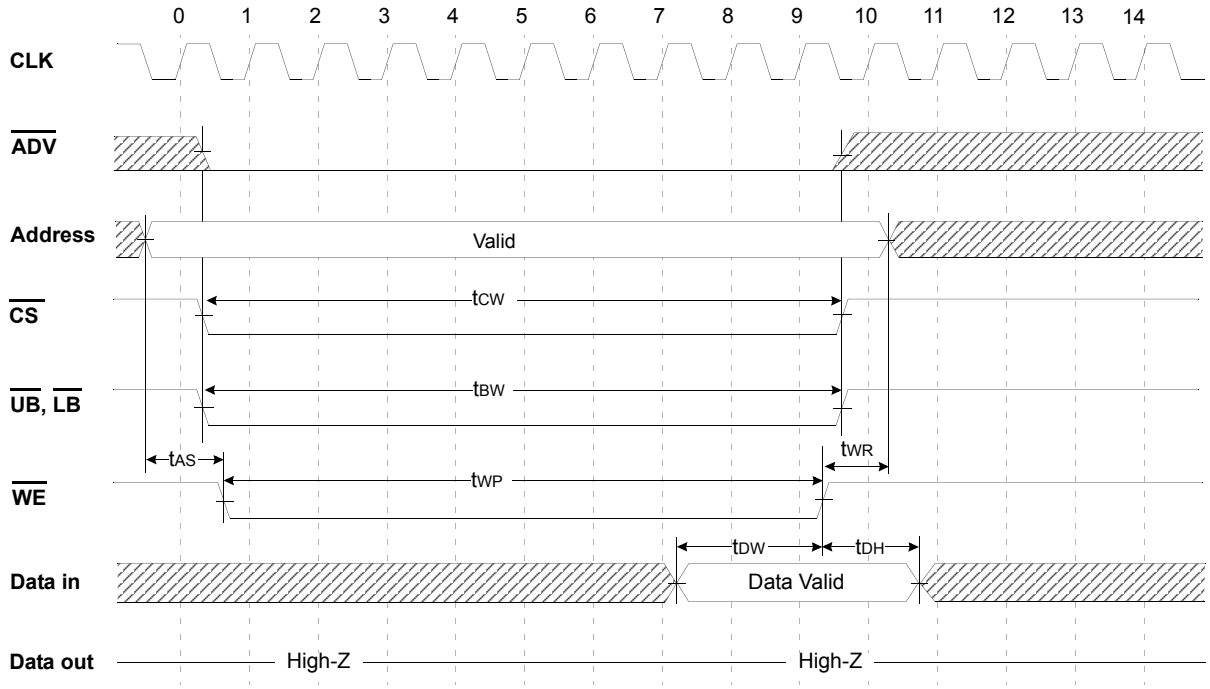
AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
tBSADV	0	-	0	-	0	-	ns	tCD	-	11	-	9	-	7	ns
tCSLH	2	-	2	-	2	-	ns	tOH(B)	2	-	2	-	2	-	ns
tCSHP	5	-	5	-	5	-	ns	tCHZ	-	10	-	10	-	10	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tBLZ	5	-	5	-	5	-	ns	tWZ	-	10	-	10	-	10	ns
tOLZ	5	-	5	-	5	-	ns								

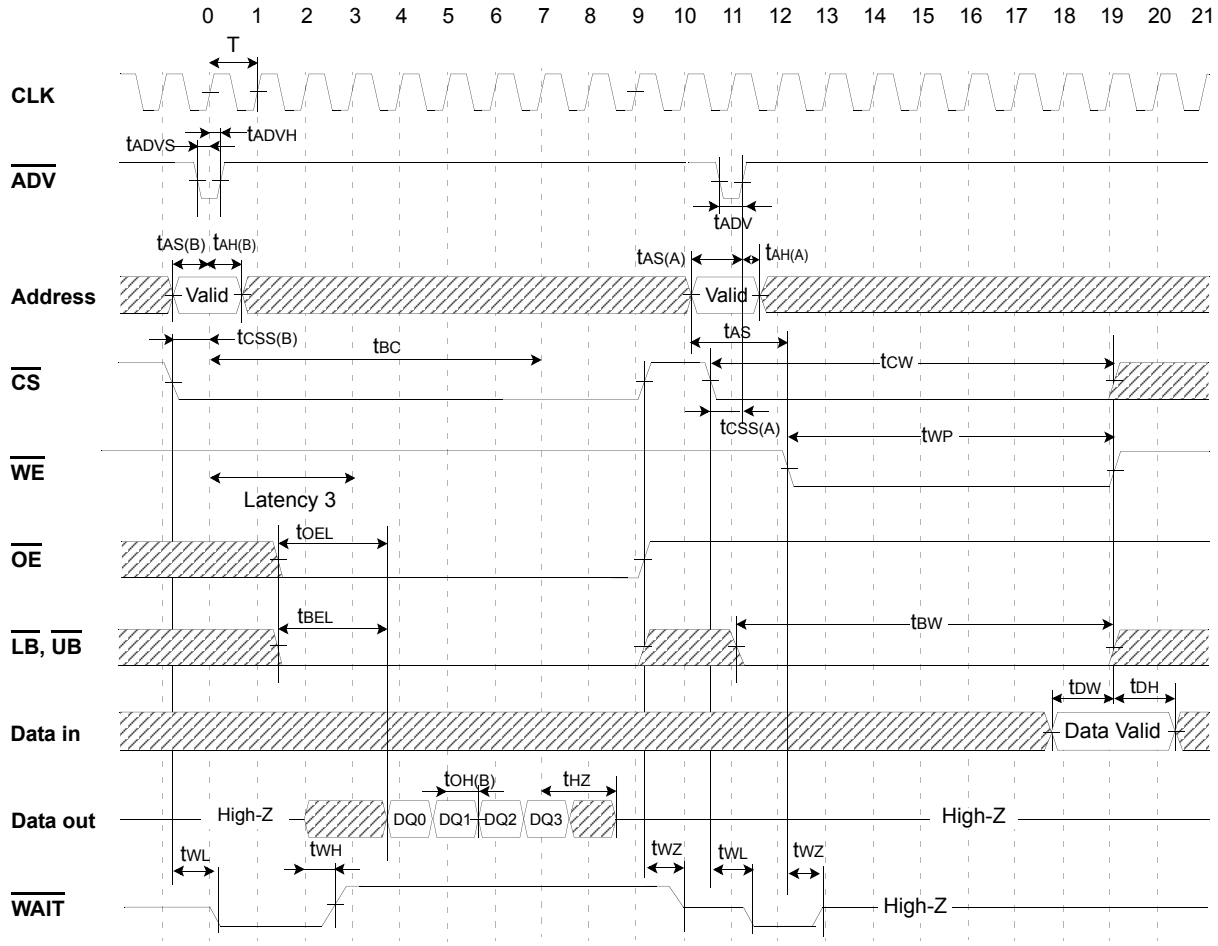
Asynch. WRITE (ADV Latch)
(PS=VIH, OE=VIH, WAIT=High-Z)



Asynch. WRITE (ADV Fix Low)
(PS=VIH, OE=VIH, WAIT=High-Z)



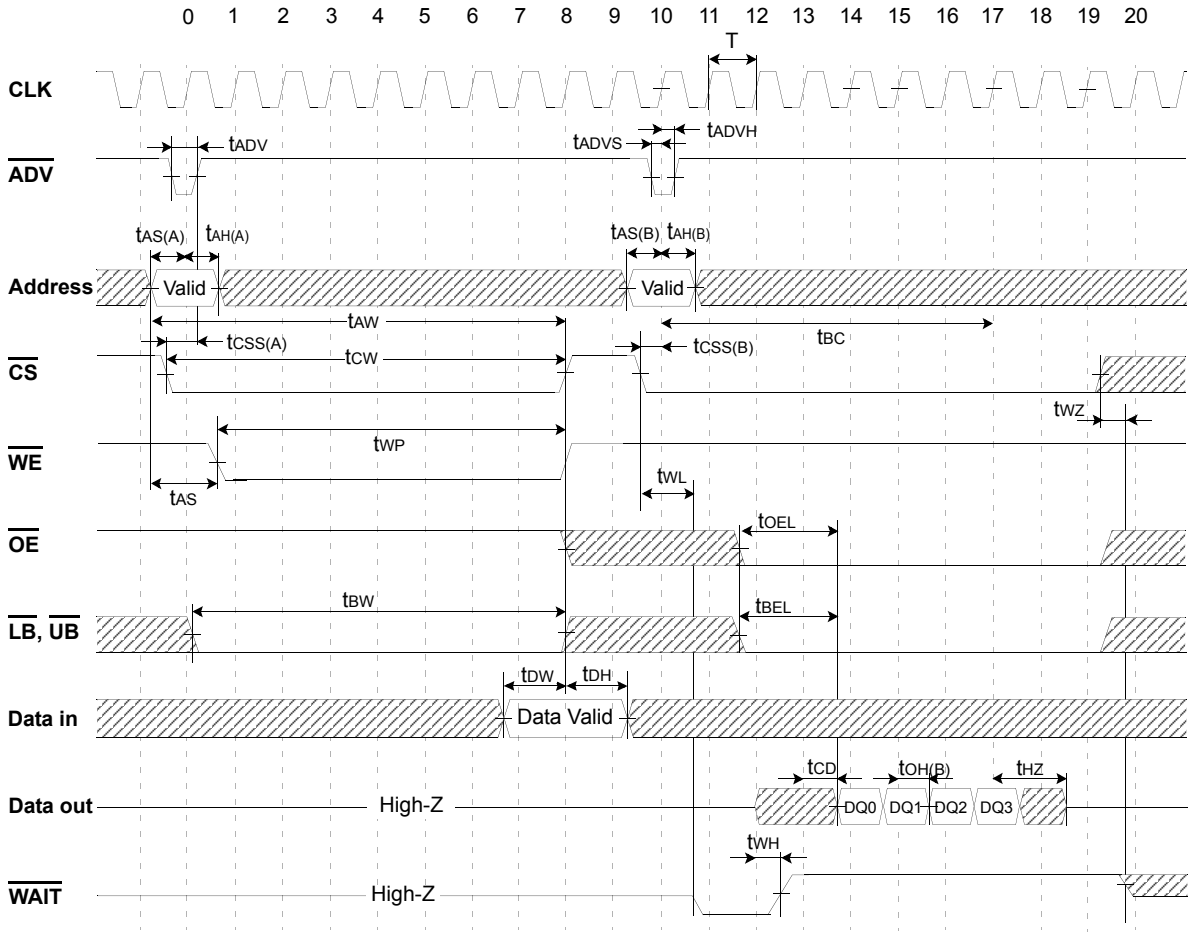
Burst READ followed by Asynch. WRITE
(PS=VIH, WAIT=High-Z, Variable Latency=3)



1. A write occurs during the overlap(t_{WP}) of low $\overline{CS}$ and low $\overline{WE}$. A write begins when $\overline{CS}$ goes low and $\overline{WE}$ goes low with asserting $\overline{UB}$ or $\overline{LB}$ for single byte operation or simultaneously asserting $\overline{UB}$ and $\overline{LB}$ for word operation. A write ends at the earliest transition when $\overline{CS}$ goes high or $\overline{WE}$ goes high. The t_{WP} is measured from the beginning of write to the end of write.
2. t_{AW} is measured from the address valid to the end of write. In this address latch type write timing, t_{WC} is same as t_{AW}.
3. t_{CW} is measured from the $\overline{CS}$ going low to the end of write.
4. t_{BW} is measured from the $\overline{UB}$ and $\overline{LB}$ going low to the end of write.

Asynch. WRITE followed by Burst READ

(PS=VIH, Variable Latency=3,Burst Length=4, WP=Low Enable, WC=one clock prior to the data)

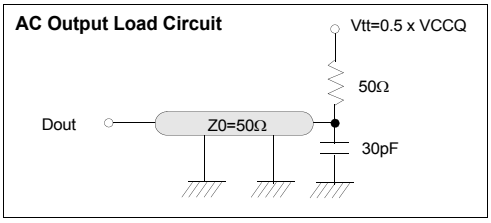


1. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
2. Multiple clock risings are allowed during low $\overline{ADV}$ period. The data starts after set Latency from the last clock rising.
3. Burst operation should not be longer than tBC(1.2μs)

MODE 3 AC OPERATING CONDITIONS (SYNCH. READ / SYNCH. WRITE)

TEST CONDITIONS

(Test Load and Test Input/Output Reference)
Input pulse level: 0.2 to VCC-0.2V
Input rising and falling time: 1ns
Input and output reference voltage: 0.5 x VCC
Output load: CL=30pF
VCC:1.7V~1.95V
TA: -40°C~85°C



AC CHARACTERISTICS

Parameter List		Symbol	66MHz		80MHz		104MHz		Units
			Min	Max	Min	Max	Min	Max	
Burst Operation (Common)	Clock Cycle Time	T	15	200	12.5	200	9.6	200	ns
	Burst Cycle Time	tBC	-	1200	-	1200	-	1200	ns
	Address Set-up Time to clock	tAS(B)	3	-	3	-	3	-	ns
	Address Hold Time from clock	tAH(B)	2	-	2	-	2	-	ns
	$\overline{ADV}$ Setup Time to clock	tADVS	3	-	3	-	3	-	ns
	$\overline{ADV}$ Hold Time from clock	tADVH	2	-	2	-	2	-	ns
	$\overline{CS}$ Setup Time to clock	tCSS(B)	3	-	3	-	3	-	ns
	$\overline{CS}$ High to New $\overline{ADV}$ Low (Burst Stop)	tBSADV	0	-	0	-	0	-	ns
	$\overline{CS}$ Low Hold Time from Clock(Burst Stop)	tCSLH	2	-	2	-	2	-	ns
	$\overline{CS}$ High Pulse Width	tCSHP	5	-	5	-	5	-	ns
	$\overline{CS}$ Low to $\overline{WAIT}$ Low	tWL	-	12	-	12	-	12	ns
	Clock to $\overline{WAIT}$ High	tWH	-	11	-	9	-	7	ns
	$\overline{CS}$ High to $\overline{WAIT}$ High-Z	tWZ	-	10	-	10	-	10	ns
Burst Read Operation	$\overline{UB}$, $\overline{LB}$ Low to End of Latency Clock	tBEL	20	-	20	-	20	-	ns
	$\overline{OE}$ Low to End of Latency Clock	tOEL	20	-	20	-	20	-	ns
	$\overline{UB}$, $\overline{LB}$ Low to Low-Z Output	tBLZ	5	-	5	-	5	-	ns
	$\overline{OE}$ Low to Low-Z Output	tOLZ	5	-	5	-	5	-	ns
	Clock Rising to Data Output	tCD	-	11	-	9	-	7	ns
	Output Hold from clock	tOH(B)	2	-	2	-	2	-	ns
	Burst End Clock to Output High-Z	tHZ	-	10	-	10	-	10	ns
	$\overline{CS}$ High to Output High-Z	tCHZ	-	10	-	10	-	10	ns
	$\overline{OE}$ High to Output High-Z	tOHZ	-	10	-	10	-	10	ns
	$\overline{UB}$, $\overline{LB}$ High to Output High-Z	tBHZ	-	10	-	10	-	10	ns

1. Refresh can not be implemented when tBSADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.2us without $\overline{CS}$ toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBSADV.
2. The High-Z timings measure a 100mV transition from either VOH or VOL toward VCCQ x 0.5
3. The Low-Z timings measure a 100mV transition away from the High-Z level toward either VOH or VOL.

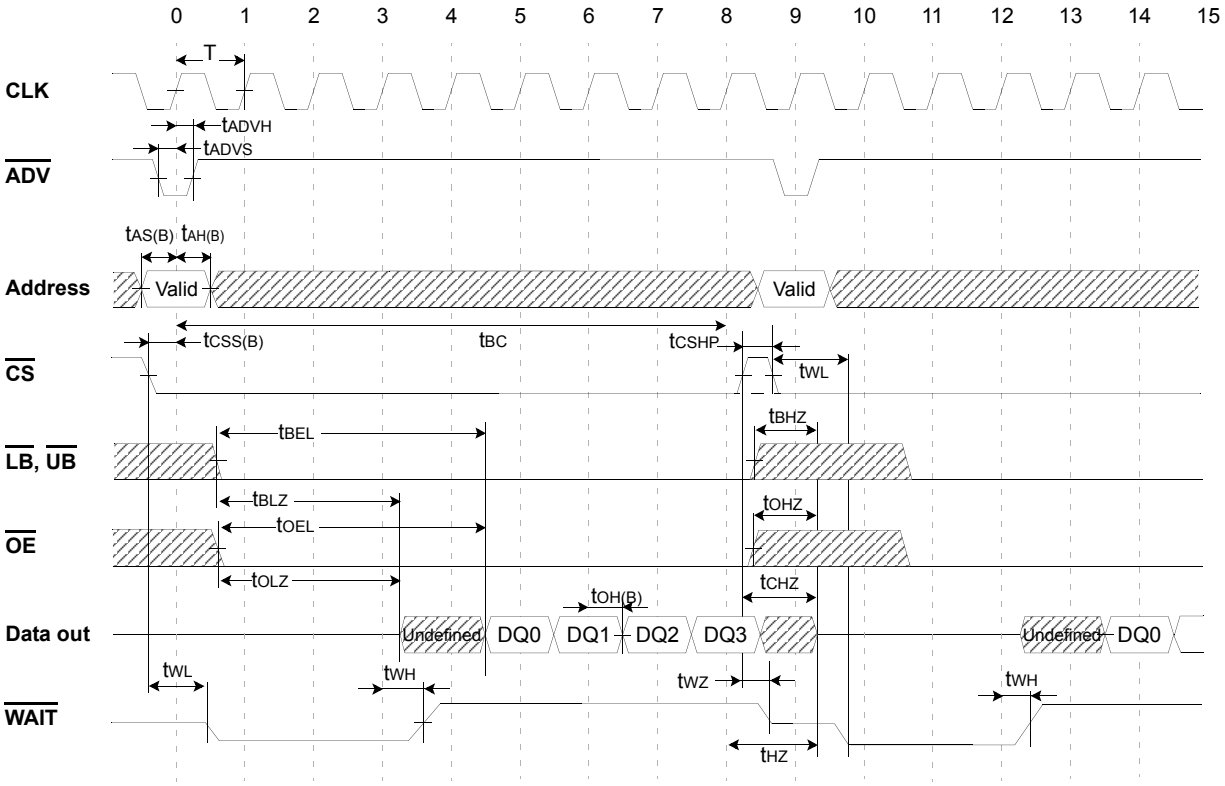
Burst Write Operation	$\overline{WE}$ Set-up Time to Clock	tWES	3	-	3	-	3	-	ns
	$\overline{WE}$ Hold Time from Clock	tWEH	2	-	2	-	2	-	ns
	$\overline{UB}$, $\overline{LB}$ Set-up Time to Clock	tBS	3	-	3	-	3	-	ns
	Burst End clock to New $\overline{ADV}$ Low	tBEADV	0	-	0	-	0	-	ns
	$\overline{UB}$, $\overline{LB}$ Hold Time from Clock	tBH	2	-	2	-	2	-	ns
	Byte Masking Set-up Time to Clock	tBMS	3	-	3	-	3	-	ns
	Byte Masking Hold Time from Clock	tBMH	2	-	2	-	2	-	ns
	Write Data Set-up Time to Clock	tDS	3	-	3	-	3	-	ns
	Write Data Hold Time from Clock	tDHC	2	-	2	-	2	-	ns

1. Refresh can not be implemented when tBEADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.2us without $\overline{CS}$ toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBEADV.

TIMING WAVEFORMS (SYNCH. READ / SYNCH. WRITE)

Burst READ - Fixed Latency

(PS=VIH, WE=VIH, WAIT=High-Z, Latency=4, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



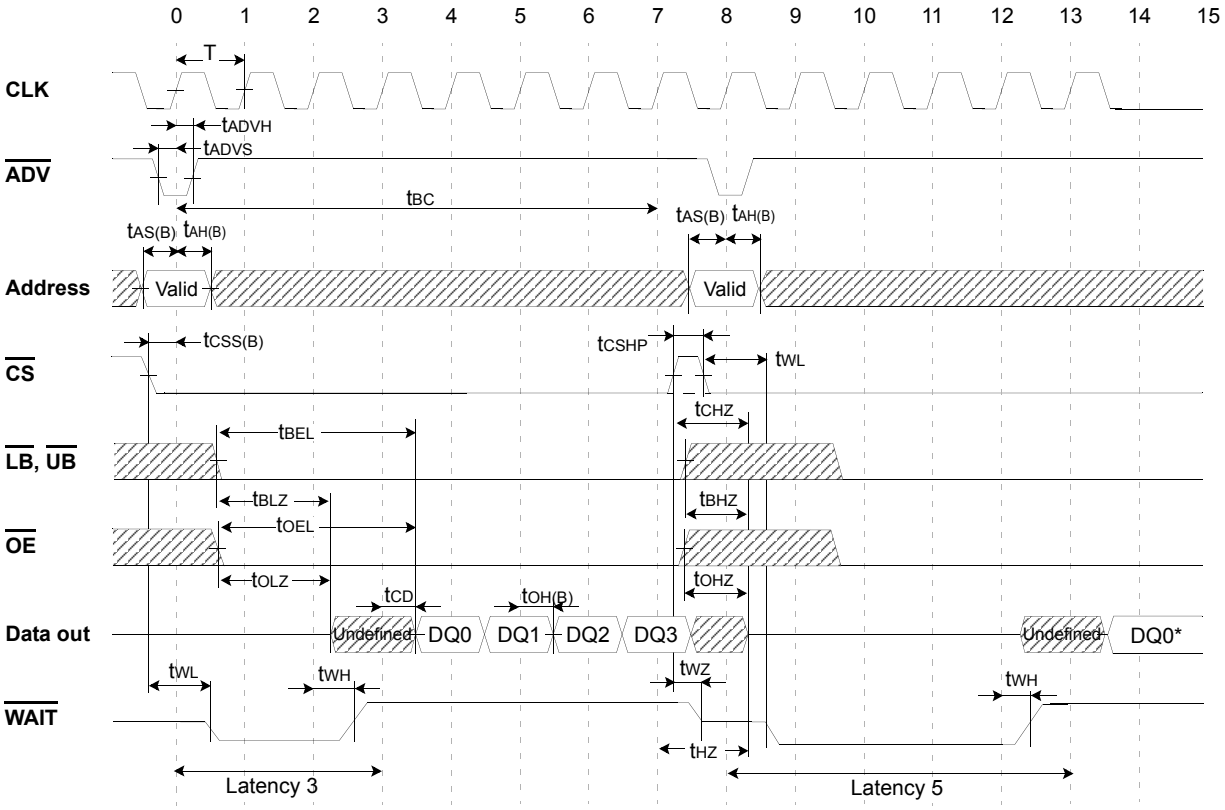
1. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
2. Multiple clock risings are allowed during low $\overline{ADV}$ period. The data starts after set Latency from the last clock rising.
3. Burst operation should not be longer than tBC(1.2μs)

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1200	-	1200	-	1200	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

Burst READ - Variable Latency

(PS=VIH, WE=VIH, Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



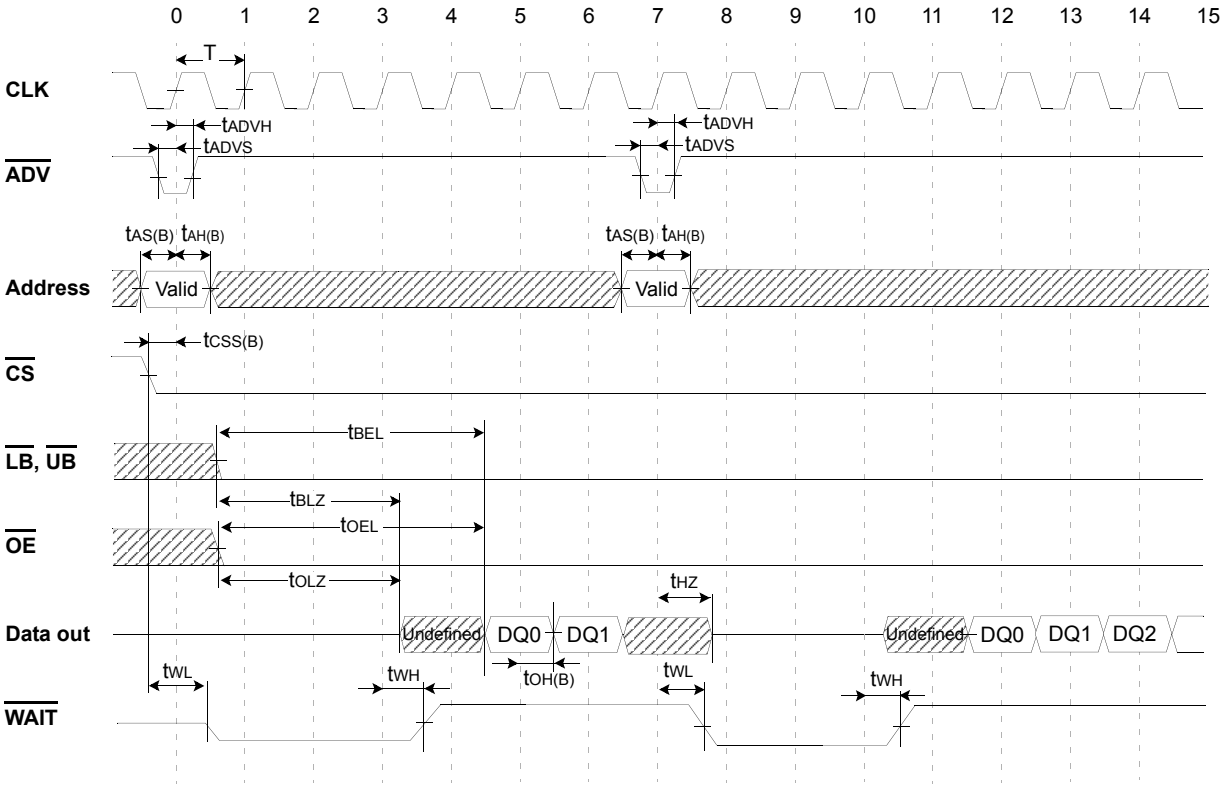
1. Delayed Latency should be taken increased when refresh is required. Refer to Latency Table.
2. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
3. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
4. Burst operation should not be longer than tBC(1.2μs).

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1200	-	1200	-	1200	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

Burst READ ($\overline{ADV}$ Interrupt) - Fixed Latency

($\overline{PS}$=VIH, $\overline{WE}$=VIH, $\overline{WAIT}$=High-Z, Latency=4, Burst Length=4, WP=Low enable, WC=one clock prior to the data)



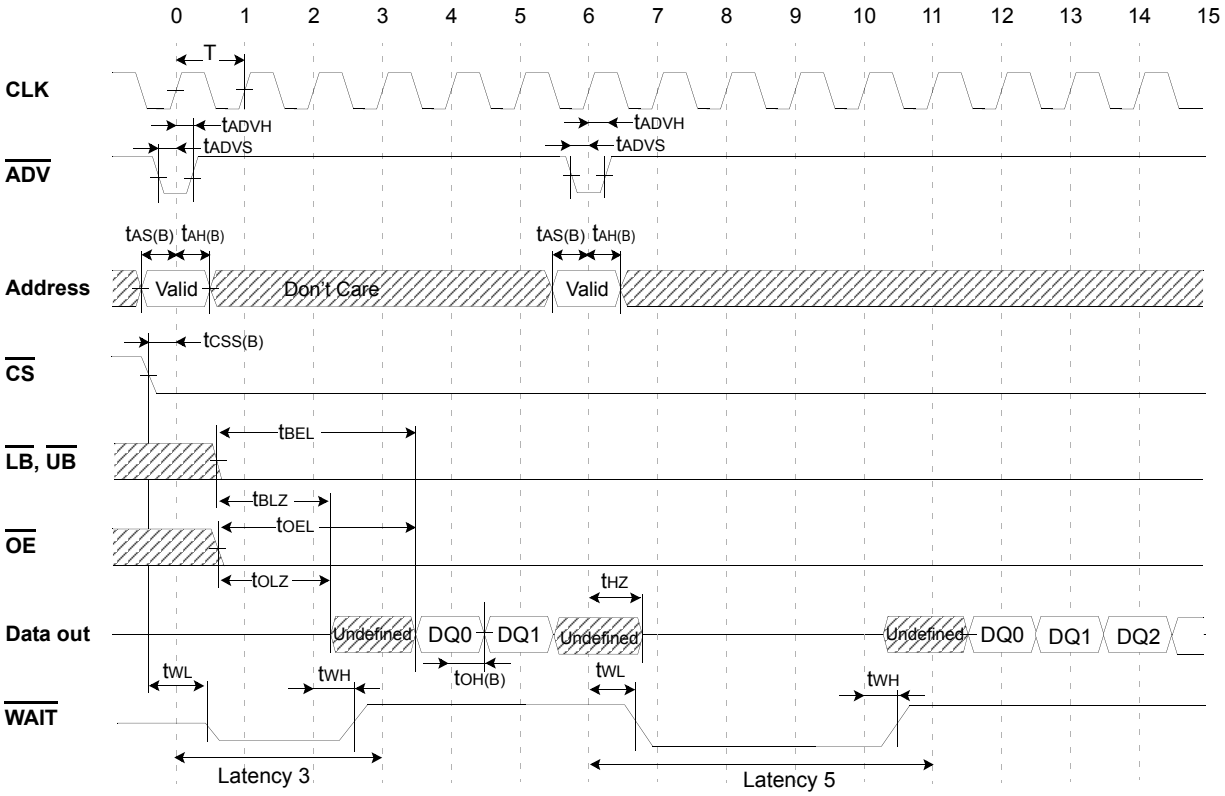
1. Refresh is blocked during $\overline{ADV}$ Interrupt Read and continuous Burst Read by ADV interrupt should not be longer than tBC (1.2us)
2. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
3. Multiple clock risings are allowed during low $\overline{ADV}$ period but the First valid data come out after set Latency from the last clock rising.
4. Burst interrupt is allowable after the first data received by controller.

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1200	-	1200	-	1200	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

Burst READ ($\overline{ADV}$ Interrupt) - Variable Latency

($\overline{PS}$=VIH, $\overline{WE}$=VIH, $\overline{WAIT}$=High-Z, Latency=3,Burst Length=4,WP=Low enable, WC=one clock prior to the data)



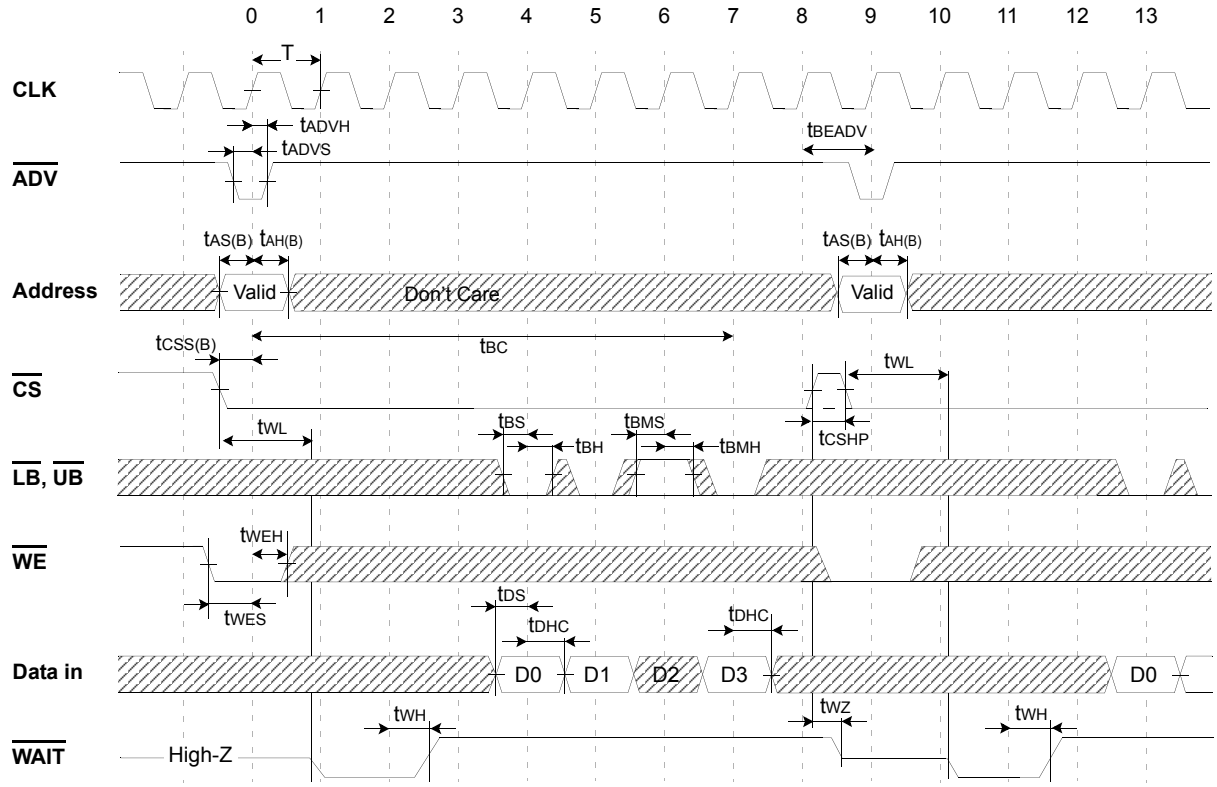
1. Delayed latency is taken for Burst READ by $\overline{ADV}$ interrupt. Refer to Latency Table.
2. Refresh is blocked during $\overline{ADV}$ Interrupt Read and continuous Burst Read by ADV interrupt should not be longer than tBC(1.2us)
3. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
4. Multiple clock risings are allowed during low $\overline{ADV}$ period. The data come out after set Latency from the last clock rising.
5. Burst interrupt is allowable after the first data received by controller.

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
T	15	200	12.5	200	9.6	200	ns	tBLZ	5	-	5	-	5	-	ns
tBC	-	1200	-	1200	-	1200	ns	tOLZ	5	-	5	-	5	-	ns
tADVS	3	-	3	-	3	-	ns	tHZ	-	10	-	10	-	10	ns
tADVH	2	-	2	-	2	-	ns	tCHZ	-	10	-	10	-	10	ns
tAS(B)	3	-	3	-	3	-	ns	tOHZ	-	10	-	10	-	10	ns
tAH(B)	2	-	2	-	2	-	ns	tBHZ	-	10	-	10	-	10	ns
tCSS(B)	3	-	3	-	3	-	ns	tCD	-	11	-	9	-	7	ns
tCSHP	5	-	5	-	5	-	ns	tOH(B)	2	-	2	-	2	-	ns
tBEL	20	-	20	-	20	-	ns	tWL	-	12	-	12	-	12	ns
tOEL	20	-	20	-	20	-	ns	tWH	-	11	-	9	-	7	ns
tWZ	-	10	-	10	-	10	ns								

Burst WRITE

(PS=VIH, OE=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



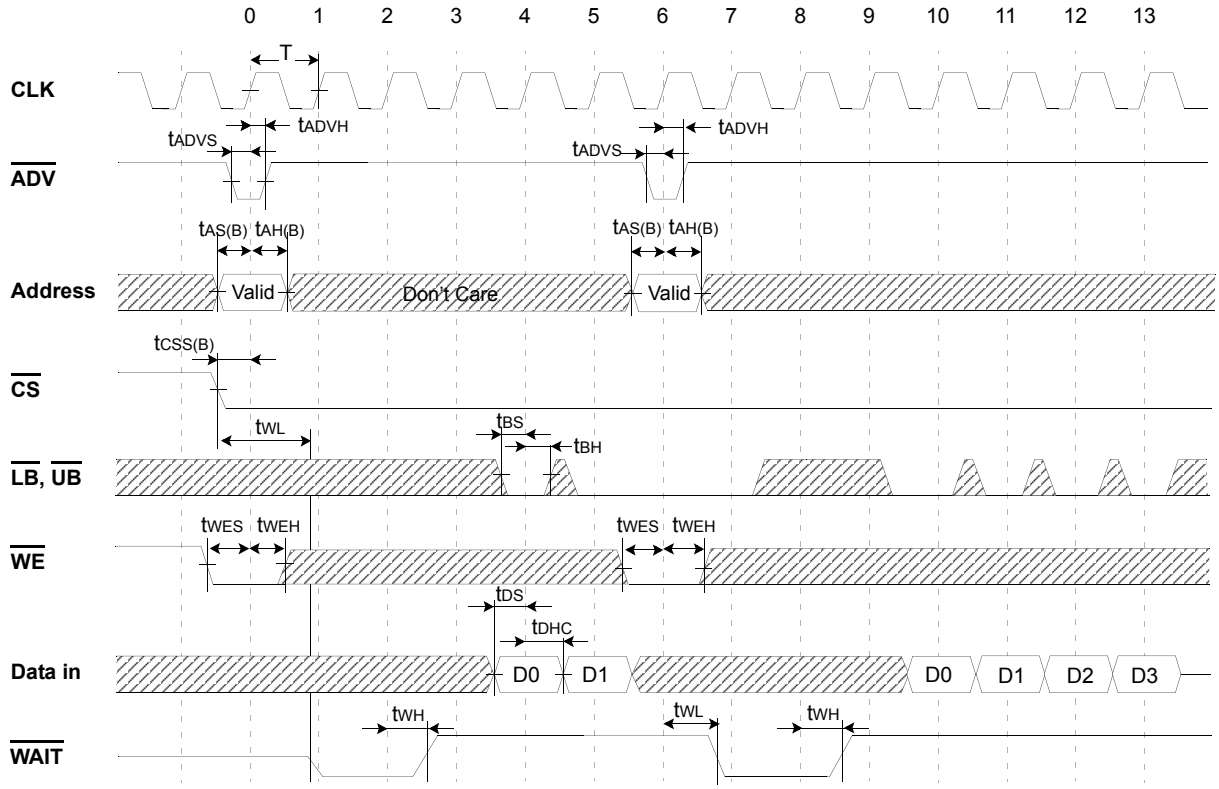
1. Refresh can not be implemented when tBEADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.2us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBEADV.
2. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
3. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.The data starts after set Latency from the last clock rising.
4. Burst operation should not be longer than tBC(1.2μs)

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
tCSHP	5	-	5	-	5	-	ns	tDS	3	-	3	-	3	-	ns
tBS	3	-	3	-	3	-	ns	tDHC	2	-	2	-	2	-	ns
tBH	2	-	2	-	2	-	ns	tWL	-	12	-	12	-	12	ns
tBMS	3	-	3	-	3	-	ns	tWH	-	11	-	9	-	7	ns
tBMH	2	-	2	-	2	-	ns	tWZ	-	10	-	10	-	10	ns
tWES	3	-	3	-	3	-	ns								
tWEH	2	-	2	-	2	-	ns								

Burst WRITE ($\overline{ADV}$ PULSE Interrupt)

($\overline{PS}$=VIH, $\overline{OE}$=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



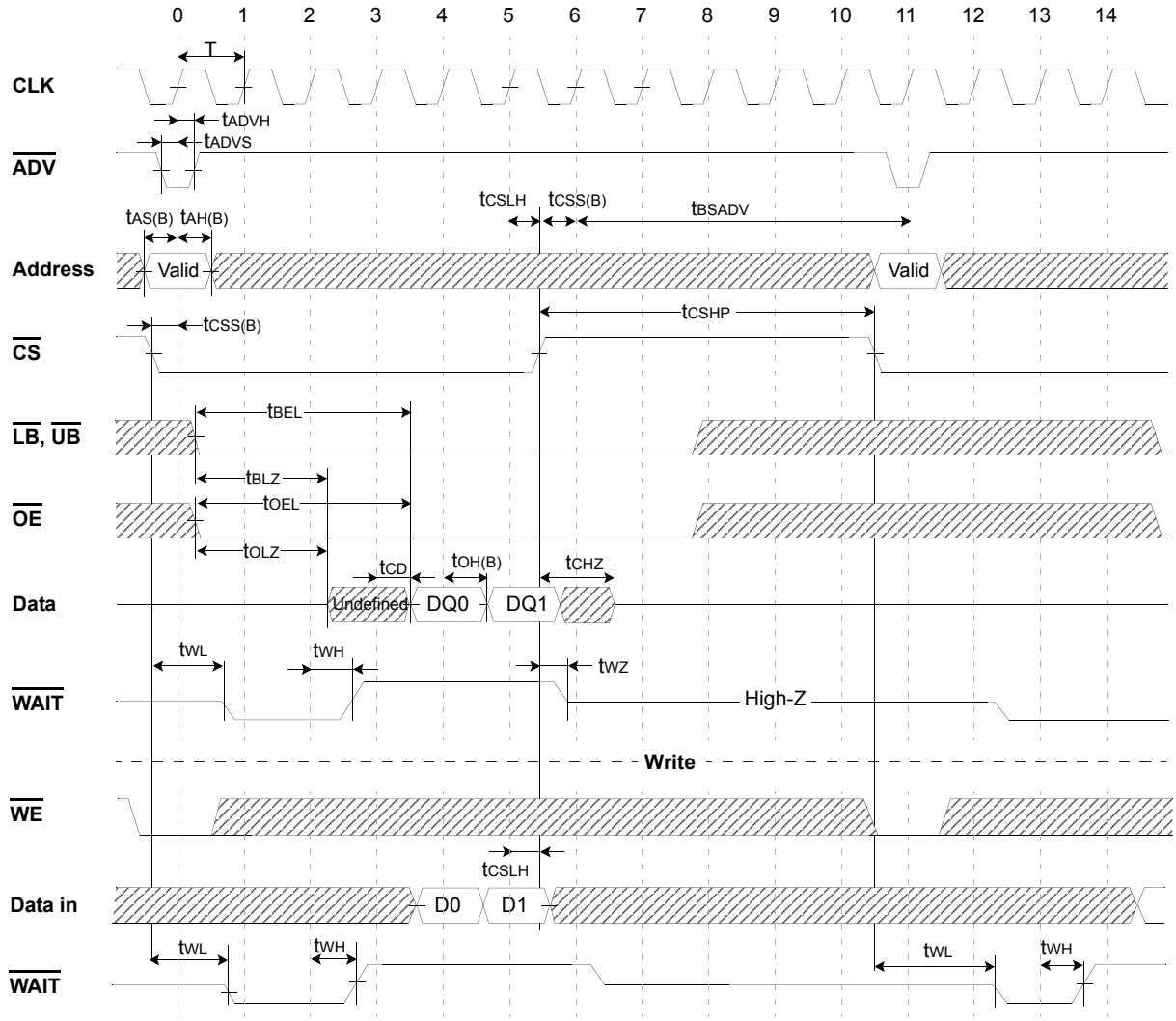
1. Multiple clock risings are allowed during low $\overline{ADV}$ period. The data starts after set Latency from the last clock rising.
2. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
3. Burst interrupt is allowable after the first data word written.

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
tCSHP	5	-	5	-	5	-	ns	tDS	3	-	3	-	3	-	ns
tBS	3	-	3	-	3	-	ns	tDHC	2	-	2	-	2	-	ns
tBH	2	-	2	-	2	-	ns	tWL	-	12	-	12	-	12	ns
tBMS	3	-	3	-	3	-	ns	tWH	-	11	-	9	-	7	ns
tBMH	2	-	2	-	2	-	ns	tWZ	-	10	-	10	-	10	ns
tWES	3	-	3	-	3	-	ns								
tWEH	2	-	2	-	2	-	ns								

Burst READ STOP & Burst WRITE STOP

(PS=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



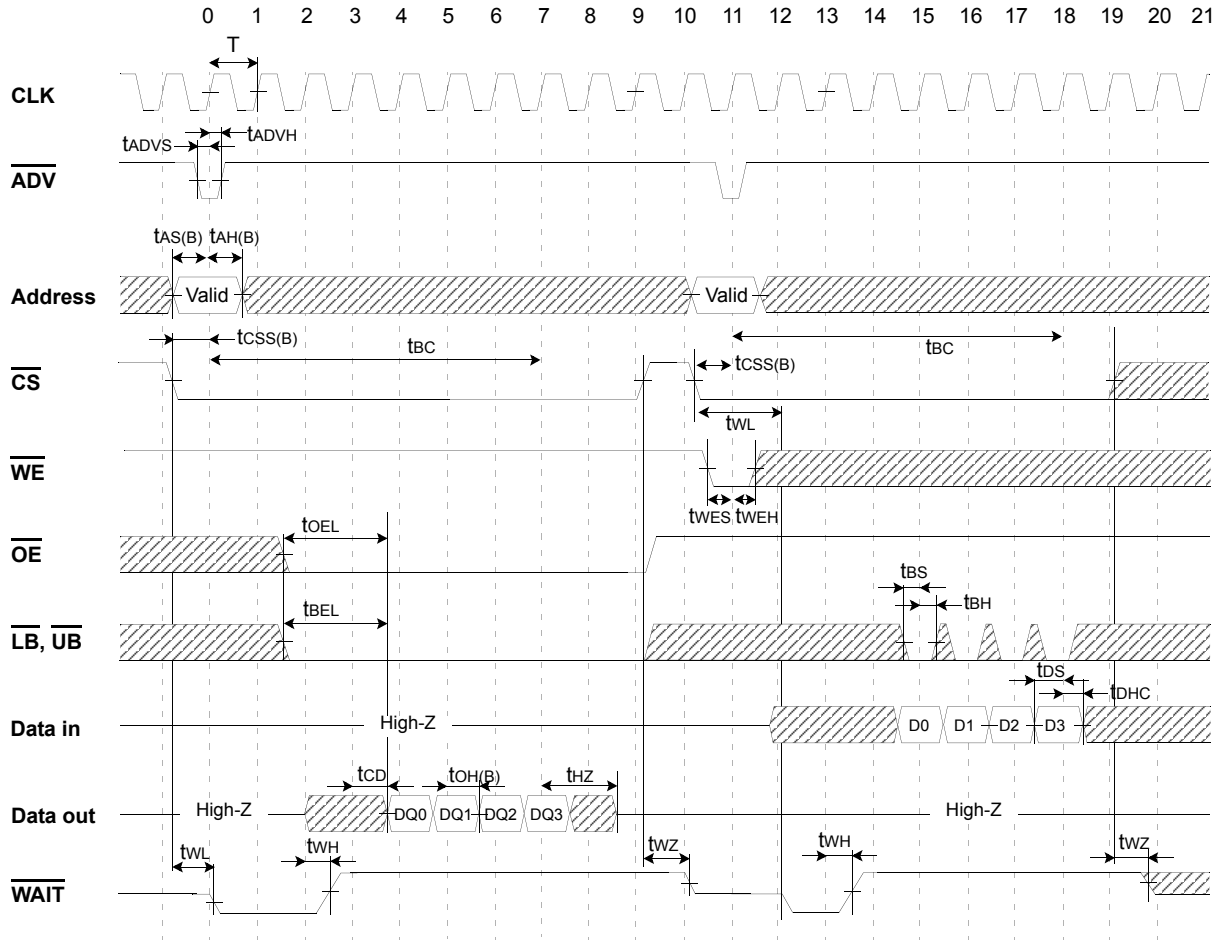
1. Refresh can not be implemented when tBEADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.2us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBEADV.
2. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
3. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)

AC CHARACTERISTICS

Symbol	66MHz		80MHz		104MHz		Units	Symbol	66MHz		80MHz		104MHz		Units
	Min	Max	Min	Max	Min	Max			Min	Max	Min	Max	Min	Max	
tCSHP	5	-	5	-	5	-	ns	tDS	3	-	3	-	3	-	ns
tBS	3	-	3	-	3	-	ns	tDHC	2	-	2	-	2	-	ns
tBH	2	-	2	-	2	-	ns	tWL	-	12	-	12	-	12	ns
tBMS	3	-	3	-	3	-	ns	tWH	-	11	-	9	-	7	ns
tBMH	2	-	2	-	2	-	ns	tWZ	-	10	-	10	-	10	ns
tWES	3	-	3	-	3	-	ns	tBSADV	-	0	-	0	-	0	ns
tWEH	2	-	2	-	2	-	ns	tOH(B)	2	-	2	-	2	-	ns

Burst READ followed by Burst WRITE

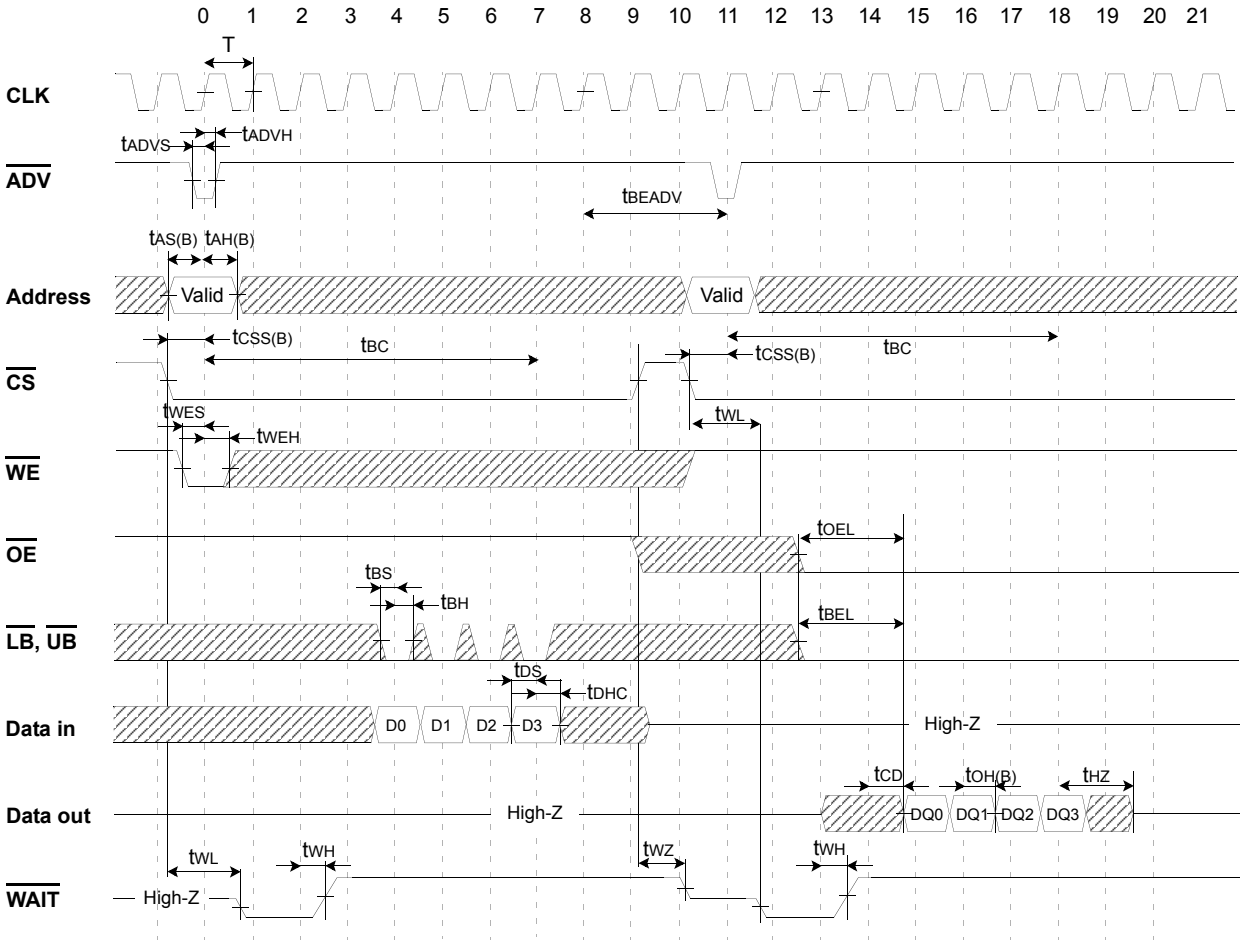
(PS=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



1. /WAIT Low(tWL) : Data not available(driven by $\overline{CS}$ low going edge or $\overline{ADV}$ low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by $\overline{CS}$ high going edge)
2. Multiple clock risings are allowed during low $\overline{ADV}$ period. The data starts after set Latency from the last clock rising.
3. Burst operation should not be longer than tBC(1.2μs)

Burst WRITE followed by Burst READ

(PS=VIH, Variable Latency=3, Burst Length=4, WP=Low Enable, WC=one clock prior to the data)



1. Refresh can not be implemented when tBEADV is in the range of 0ns ~ 13ns. It may cause Refresh fail to use the device under that condition over 1.2us without CS toggling. To avoid Refresh fail, 13ns for all frequency is needed for tBEADV.
2. /WAIT Low(tWL) : Data not available(driven by CS low going edge or ADV low going edge)
   /WAIT High(tWH) : Data available(driven by Latency-1 clock)
   /WAIT High-Z(tWZ) : Data don't care(driven by CS high going edge)
3. Multiple clock risings are allowed during low ADV period. The data starts after set Latency from the last clock rising.
4. Burst operation should not be longer than (tBC)1.2μs.